
Moscow University Seminar

February 14, 2013

Atomic Structures and Chemistry of Materials Interface

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WPI Advanced Institute for Materials Research, Tohoku University*



*Environment
Energy*



Sensor



Liquid Crystal

Chip Coil

Thermistor

Safety

IT

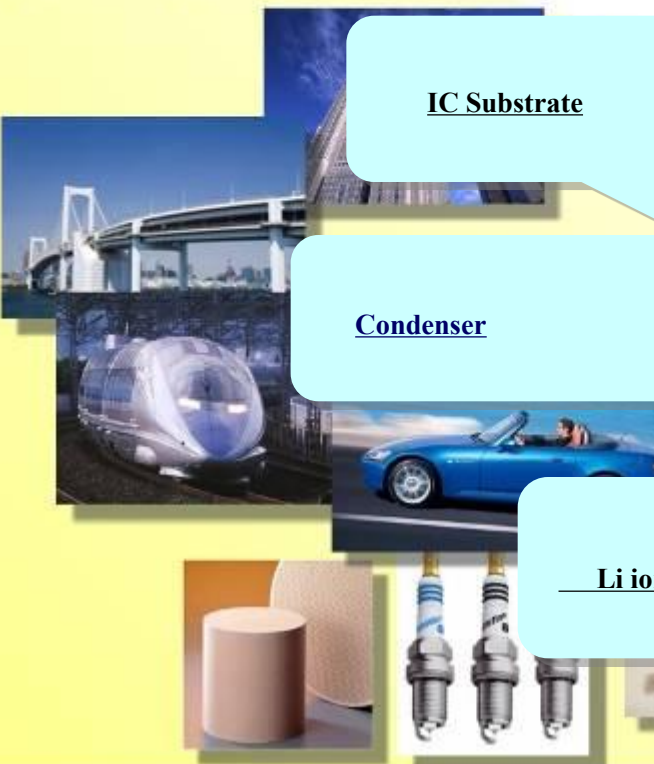
IC Substrate

Varistor

Condenser

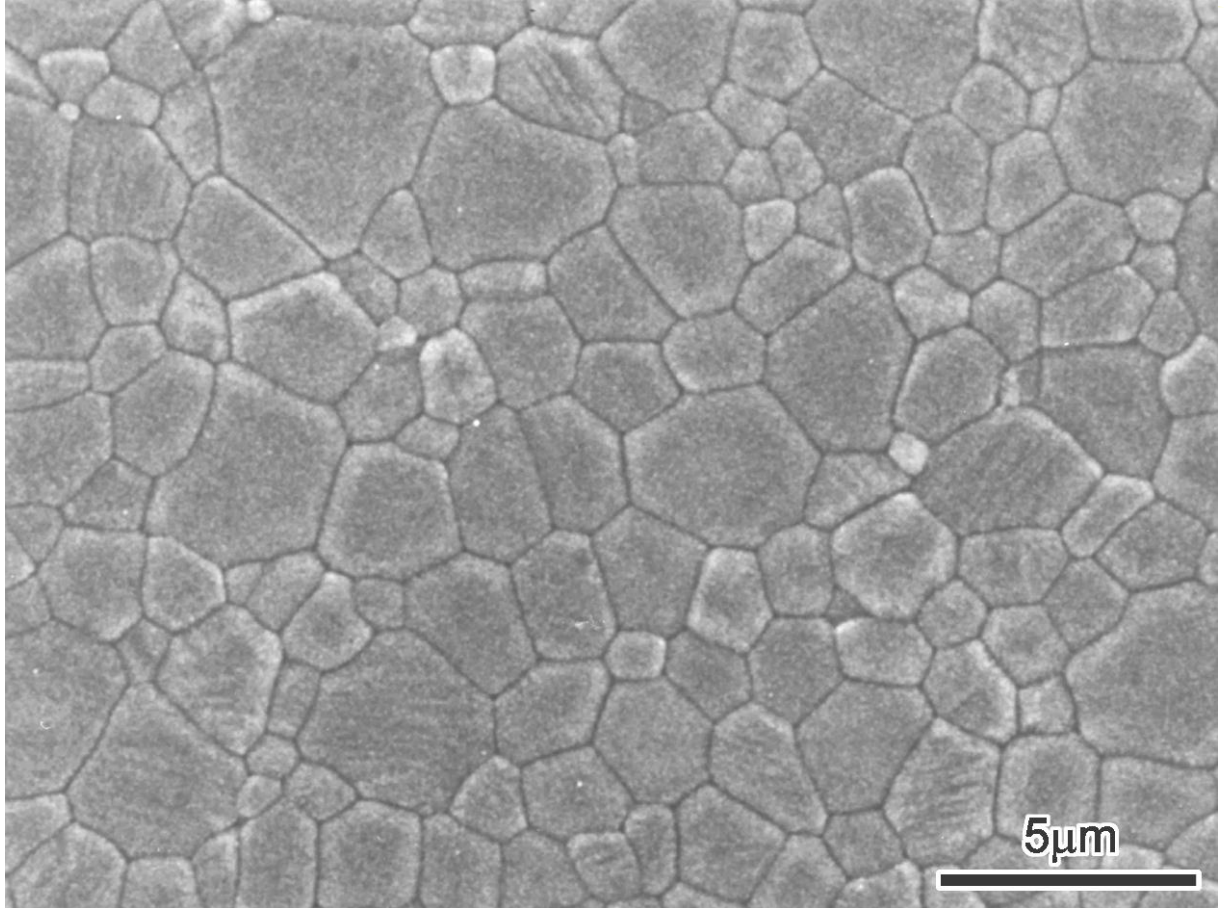
Dielectric

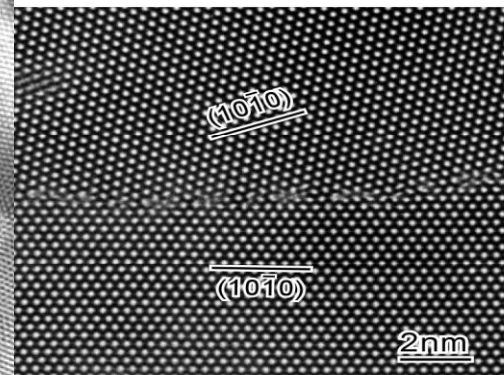
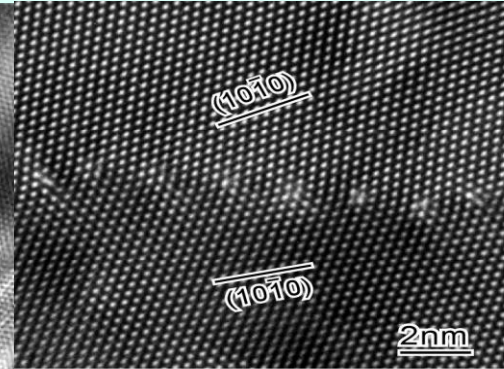
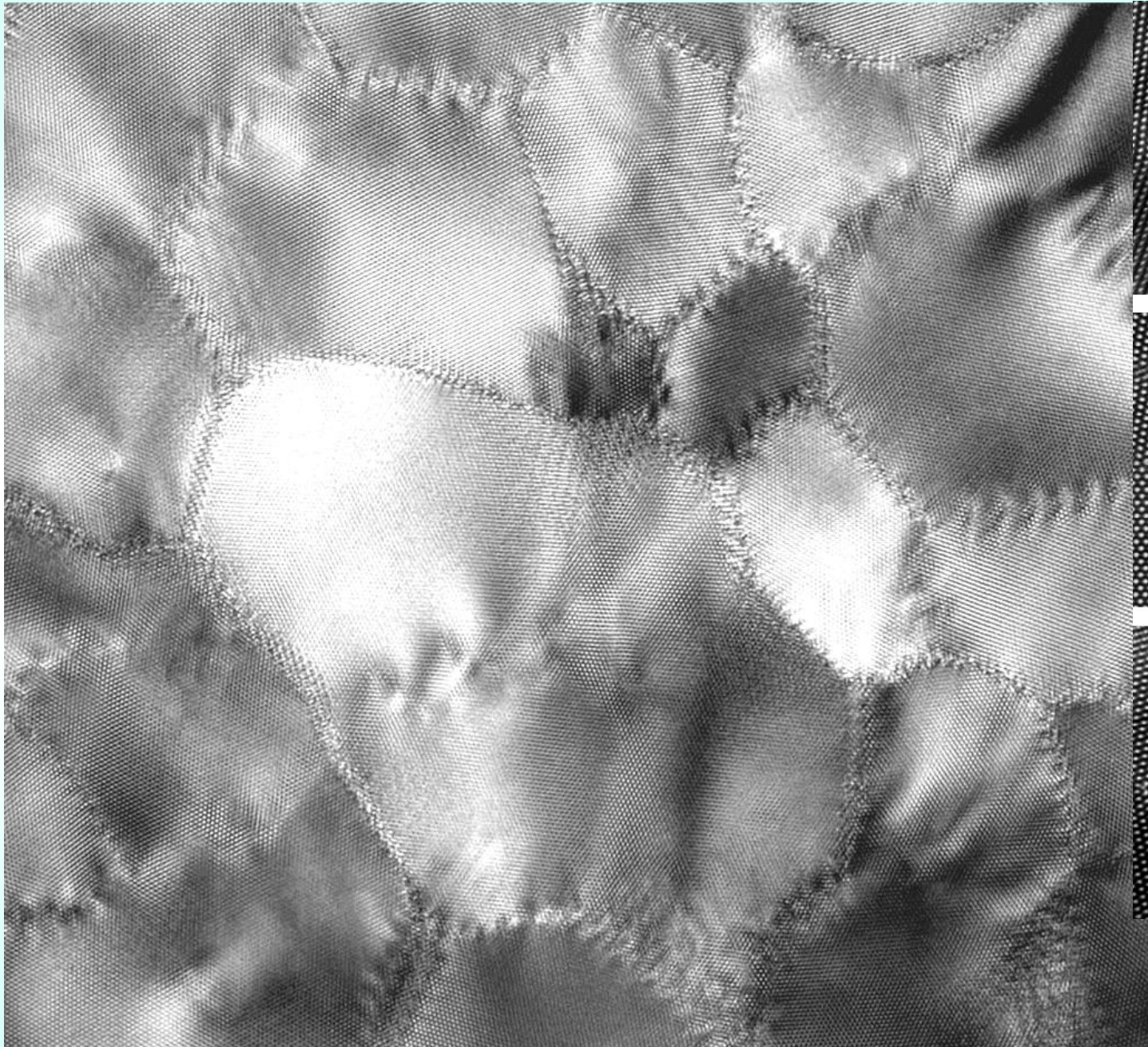
Li ion battery





Polycrystals – Grain Boundary





Dopant Effect

Varistor (ZnO)

Device to protect from static electricity and mechanical shock

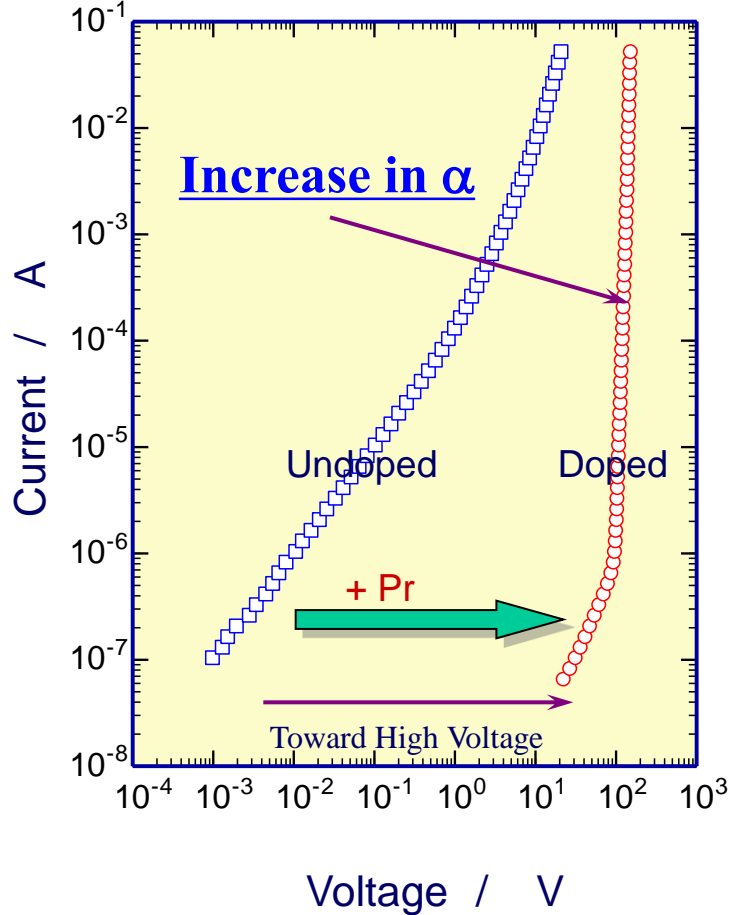


Electro devices

~0.2mol%-Pr doping



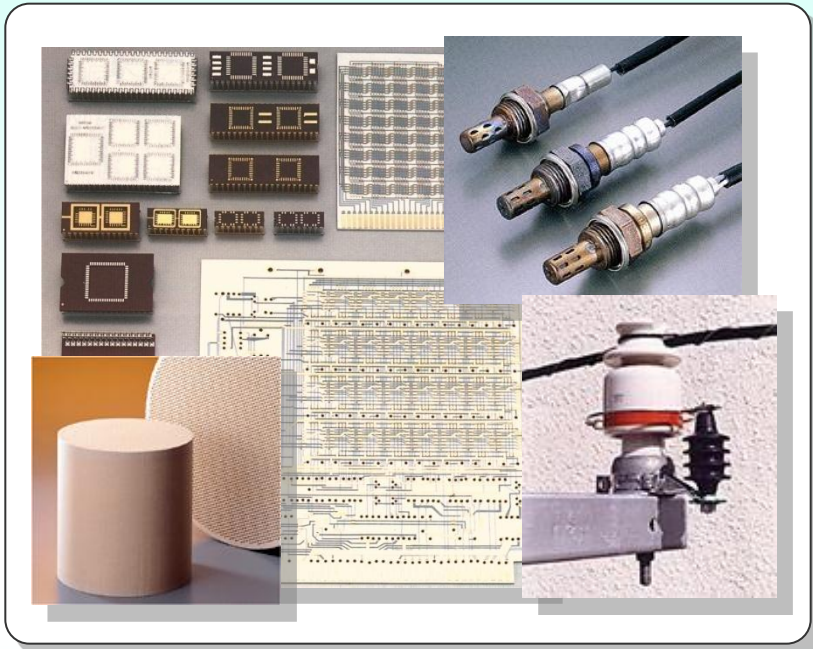
Great Improvement of Varistor Properties



Dopant Effect

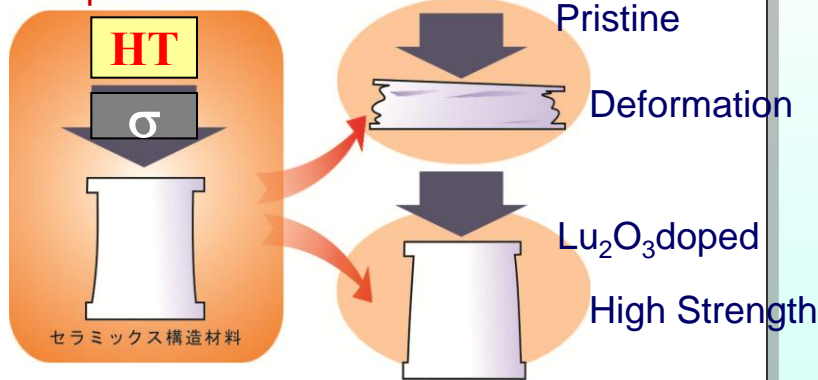
Alumina (Al_2O_3)

Structural Ceramics for IC chip substrate, Insulator, Catalyst carrier



High Temperature Ceramics

Creep Test

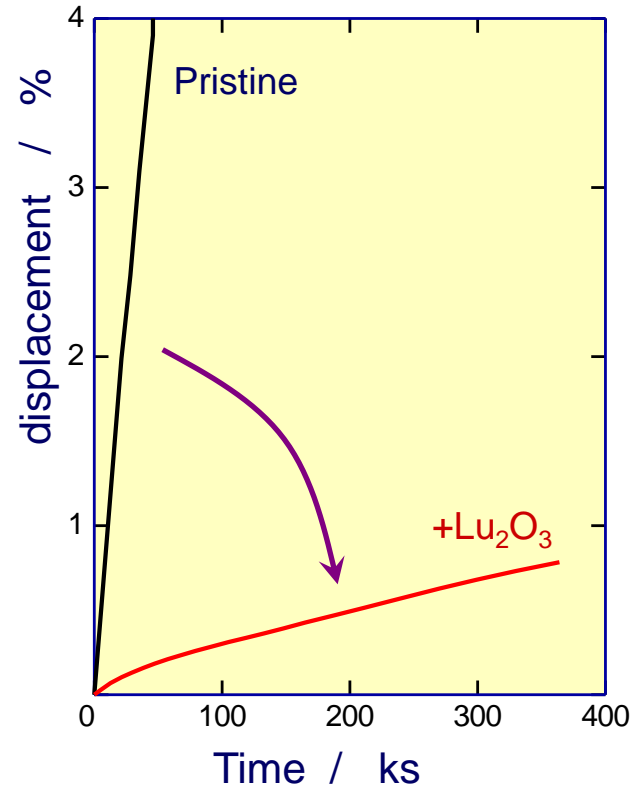


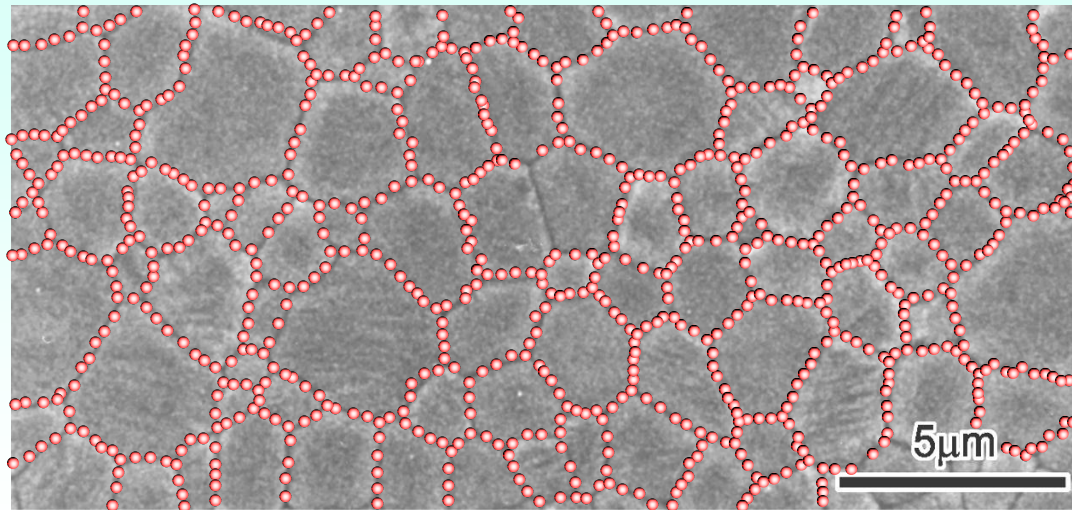
0.05mol% rare-earth doping



Improvement of Creep resistance by doping Lu_2O_3 (X100)

Creep Curve, 1250°C, 50MPa





Grain Boundary Segregation



Properties of Materials

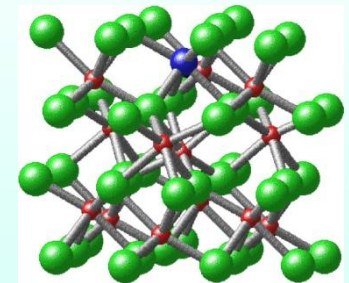
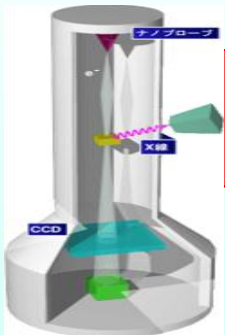
GB Segregation Behavior

Atomic
Characterization



Theoretical
Calculation

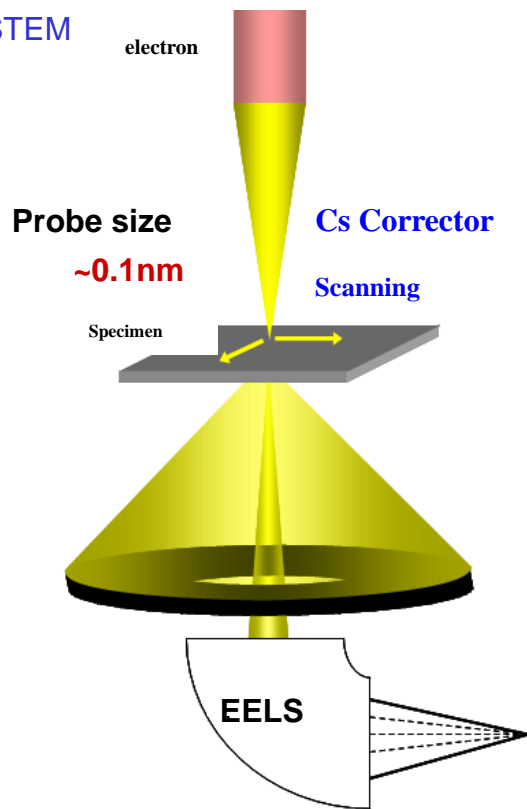
Atomic Structure around GB including dopants
Electronic Structure which is related to Properties



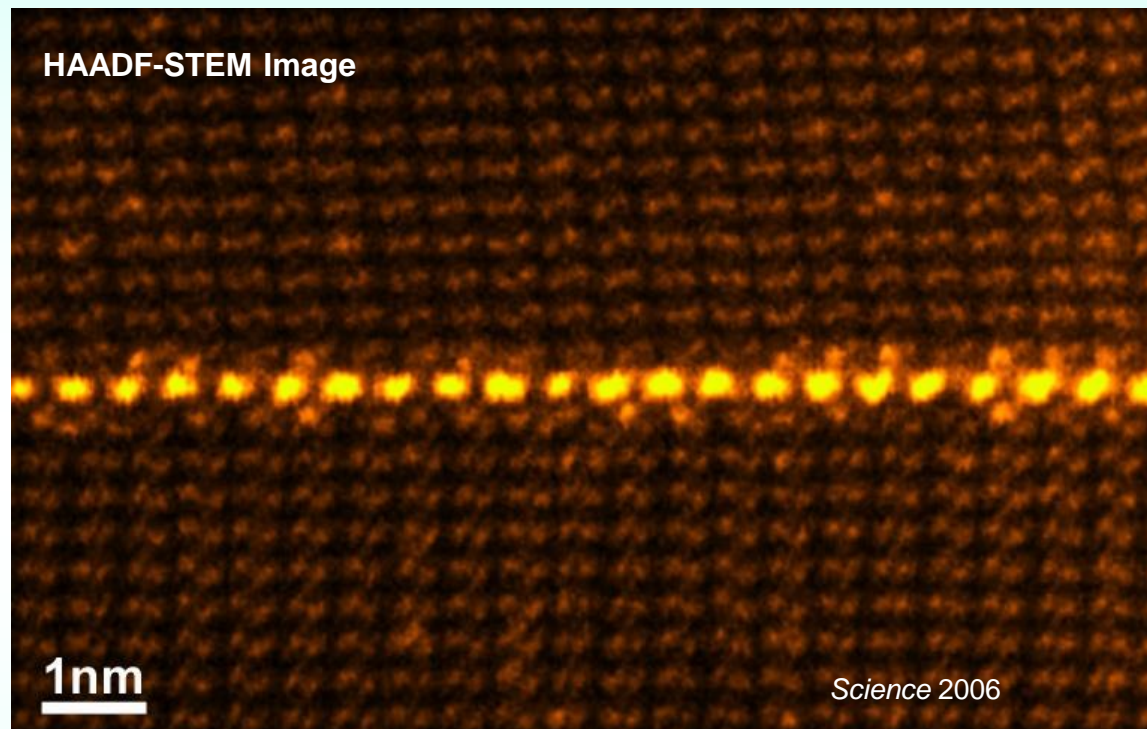
Breakthrough in Electromicroscopy (Cs corrected STEM)

HAADF-STEM (High Angle Annular Dark Field-STEM)
(Z-Contrast Imaging)

STEM



Lu₂O₃-doped Al₂O₃



Direct Observation of Segregated Dopant

$$I \propto Z^2$$

JEM-ARM200F



Specification

Item	JEM-ARM200F	Note
Acc.Voltage	120,200kV	
Resolution		
TEM		
Point	0.11nm	Cs Corrected
Lattice	0.10nm	
Information Limit	0.10nm	
STEM		
DF-Image	0.08nm	Cs Corrected
BF-Image	0.14nm	
Power Stability		
Acc.Voltage	$1 \times 10^{-6} / \text{min}$	
OL Current	$5 \times 10^{-7} / \text{min}$	

STEM-Theoretical Calculation-Materials Design

(1) Segregated Dopants at Ceramic Grain Boundaries

- Single dopant ($\text{Al}_2\text{O}_3 : \text{Y}^{3+}$)*
- Co-dopant ($\text{Al}_2\text{O}_3 : \text{Ca}^{2+} + \text{Si}^{4+}$)*
- Functional materials ($\text{ZnO} : \text{Pr}$)*

(2) Catalyst (Au-nanoparticle on TiO_2)

(3) STEM Annular Bright Field Imaging Direct Observation of Li Ions and H (LiMn_2O_4 , LiCoO_2 , VH_2)

STEM Characterization

JEOL 2100F with Cs corrector

ARM 200

STEM-Theoretical Calculation-Materials Design

(1) Segregated Dopants at Ceramic Grain Boundaries

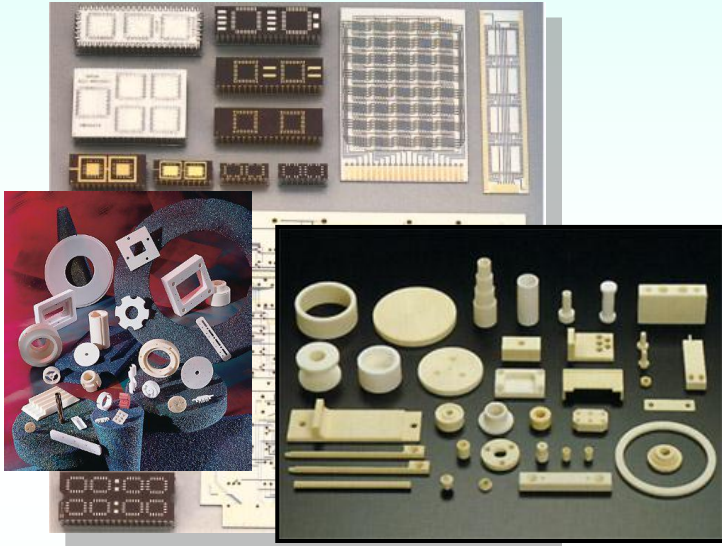
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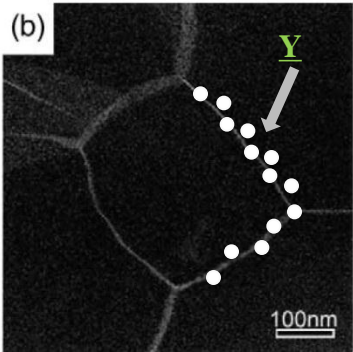
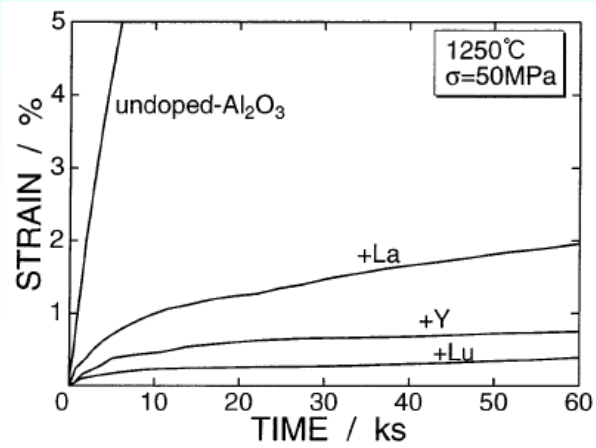
(3) STEM Annular Bright Field Imaging Direct Observation of Li Ions and H (LiMn_2O_4 , LiCoO_2 , VH_2)

Introduction

α -Al₂O₃ Ceramics



High temperature properties of α -Al₂O₃

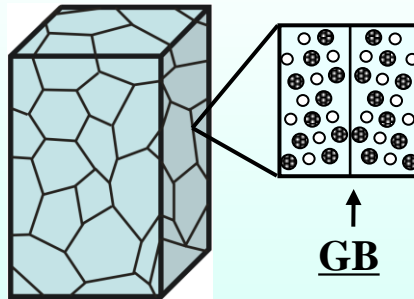


Yoshida, H. et.al., *J. Mater. Res.*, (1997)

<http://www.asuzac-ceramics.jp/material/material1.htm>

High temperature structural materials

➔ High temperature properties

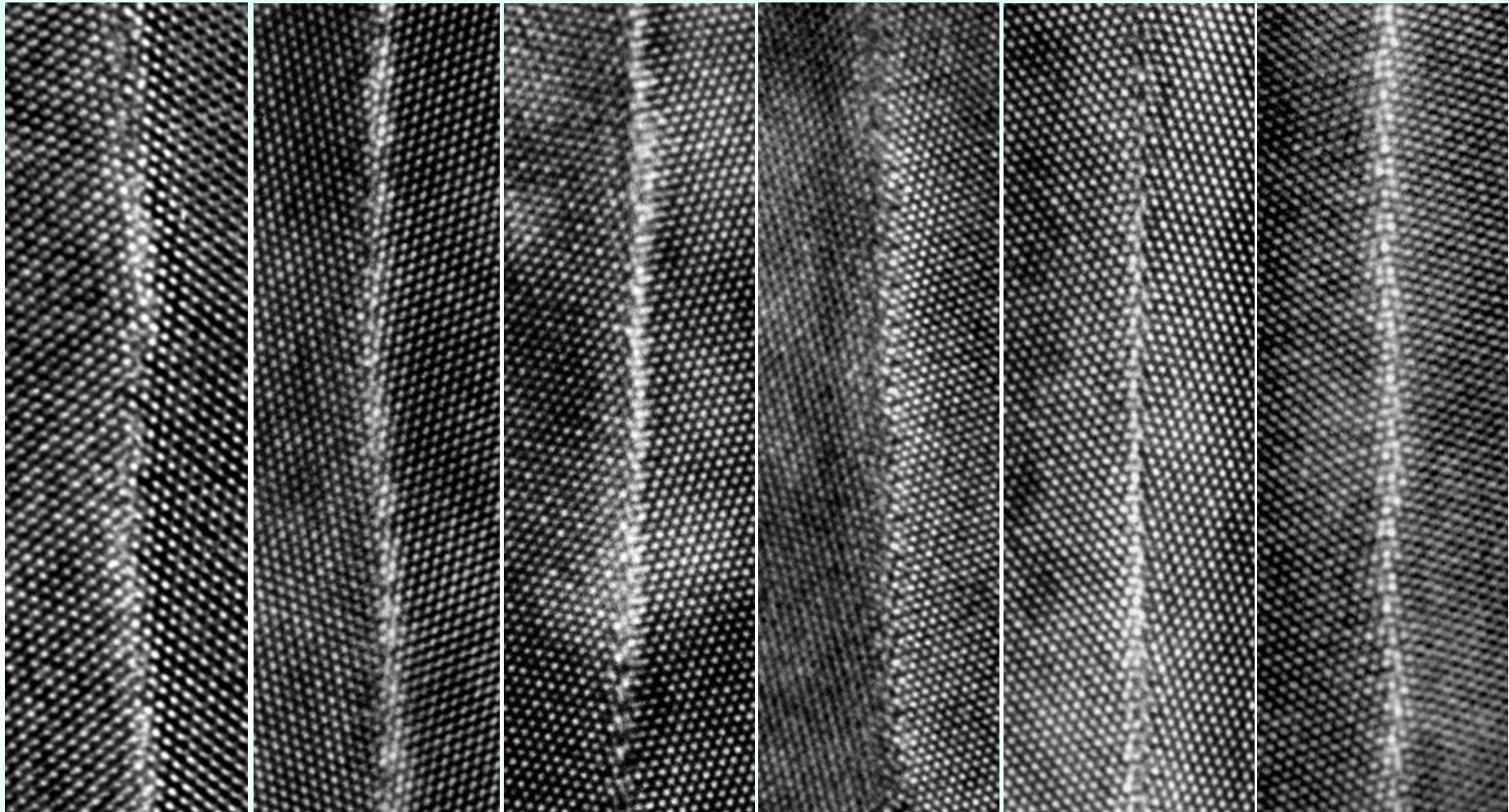


G.B.- segregated dopants enhance the high temperature creep resistance



Atomic scale understanding of G.B. segregation is important

Various types of Grain Boundaries



$\Sigma 31 / \{711\bar{4}0\}$

$\Sigma 21 / \{23\bar{1}0\}$

$\Sigma 7 / \{45\bar{1}0\}$

$\Sigma 13 / \{57\bar{2}0\}$

$\Sigma 21 / \{45\bar{1}0\}$

$\Sigma 7 / \{23\bar{1}0\}$

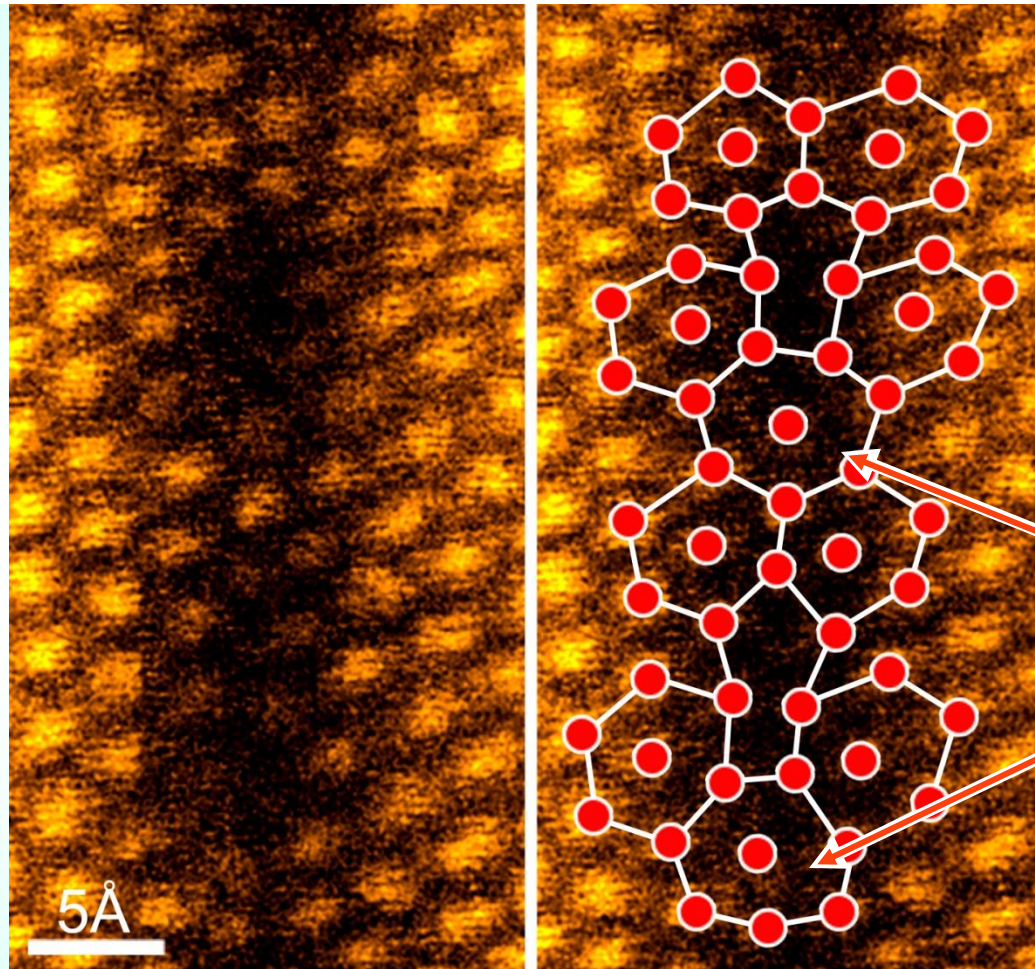
⊙ $[0001]$

2 nm

HAADF-STEM Image of Alumina $\Sigma 31$ Grain Boundary

JEOL2100F
U.Tokyo

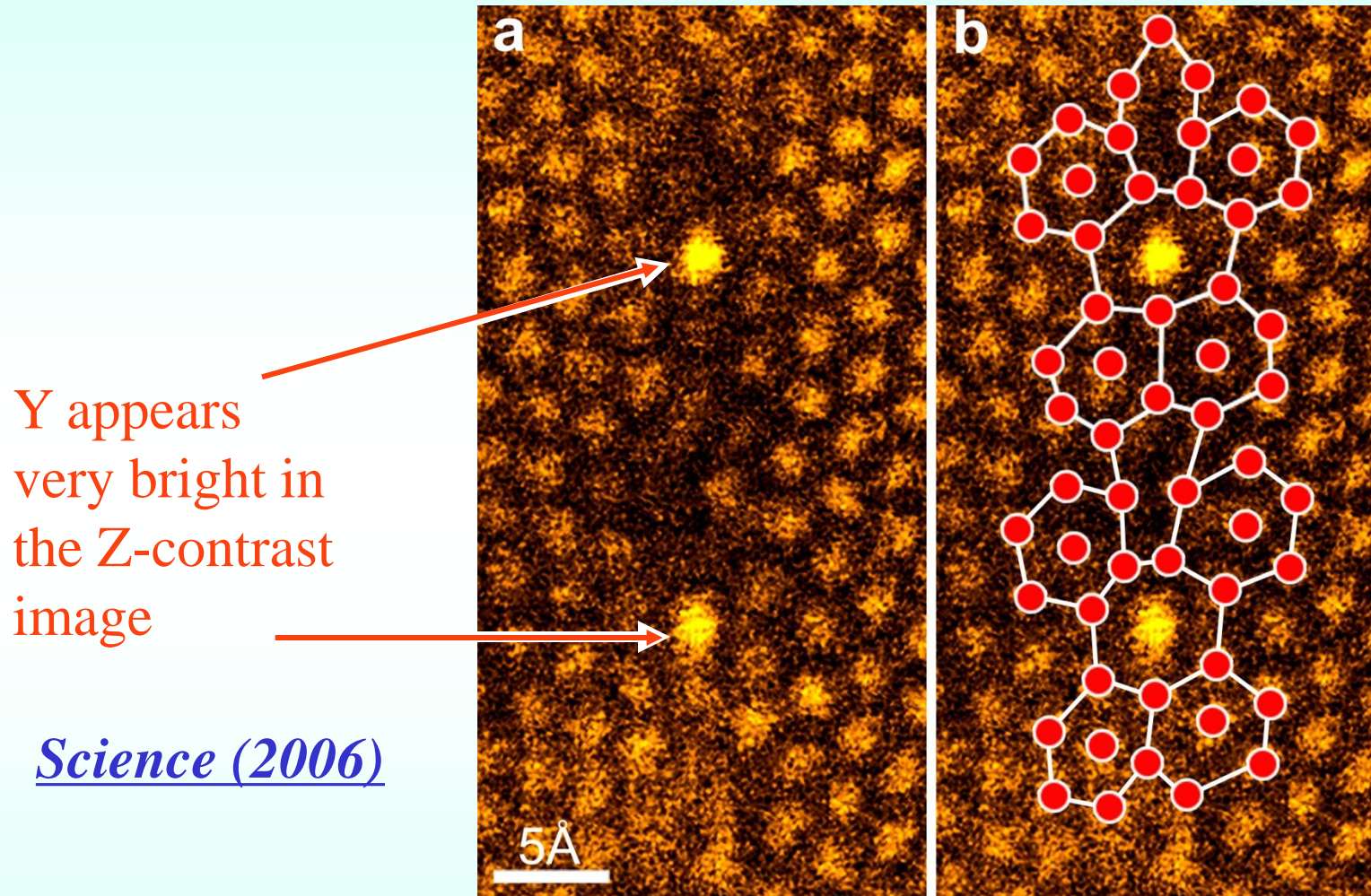
Al_2O_3



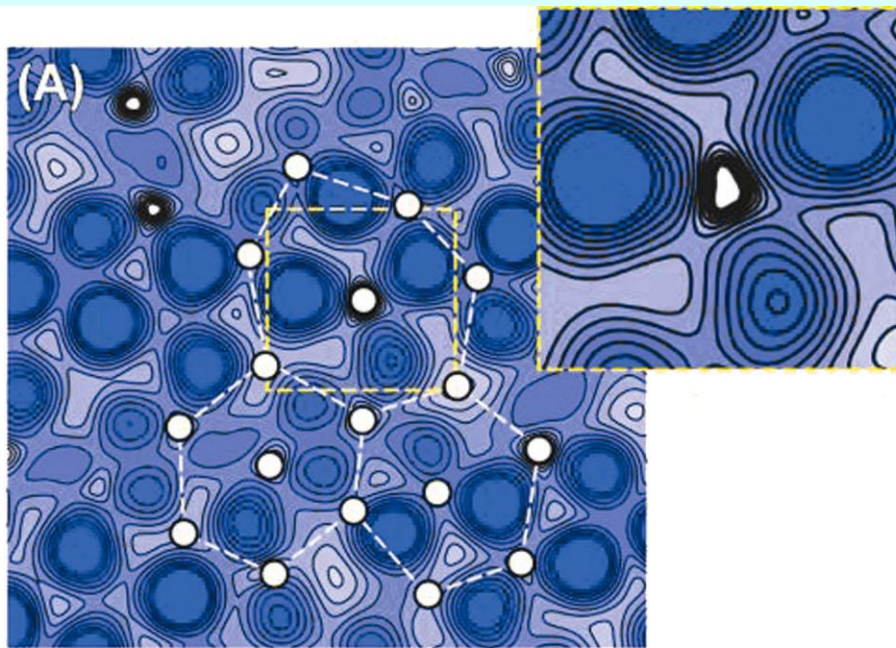
7-member
rings

The Al cation sublattice atomic structure is revealed in the STEM image, showing the presence of 7-membered ring structures.

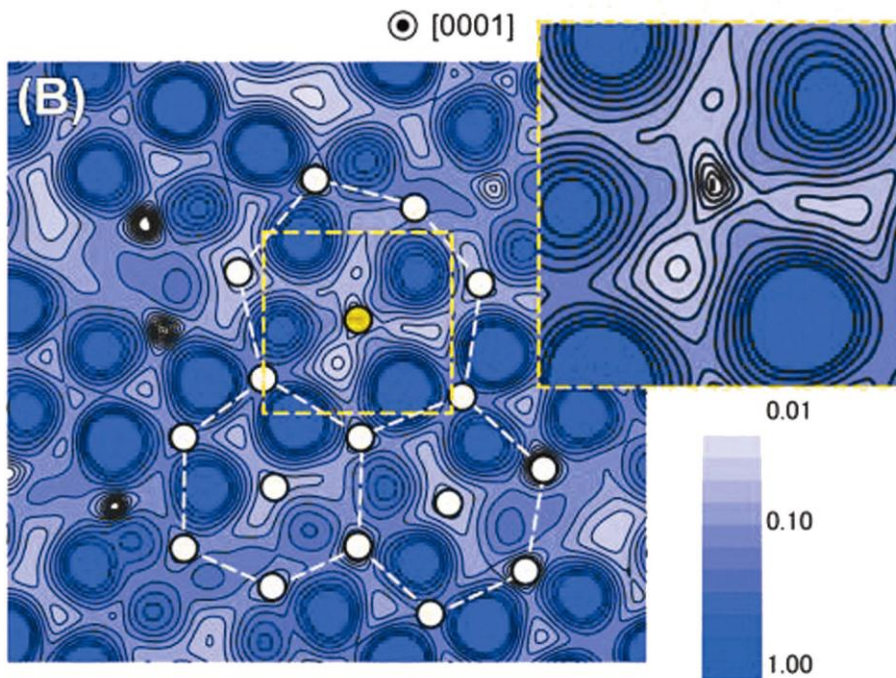
HAADF-STEM Image of the $\Sigma 31$ Y-doped Boundary



The basic grain boundary structure is relatively unaltered in comparison to the undoped case. The location of the Y ions are revealed by the STEM image



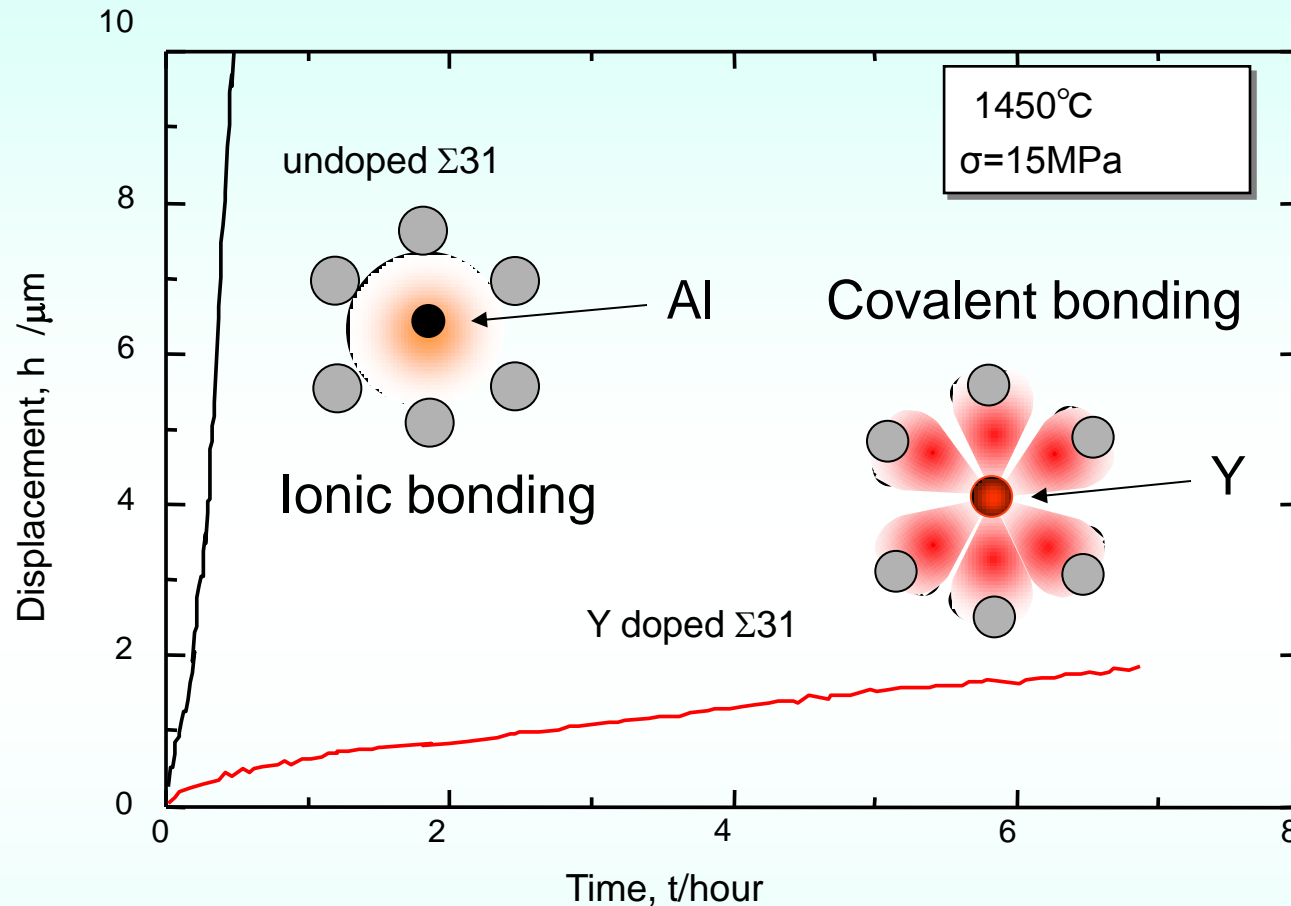
Pristine GB
Ionic Bonding



Y-doped GB
Covalent Bonding

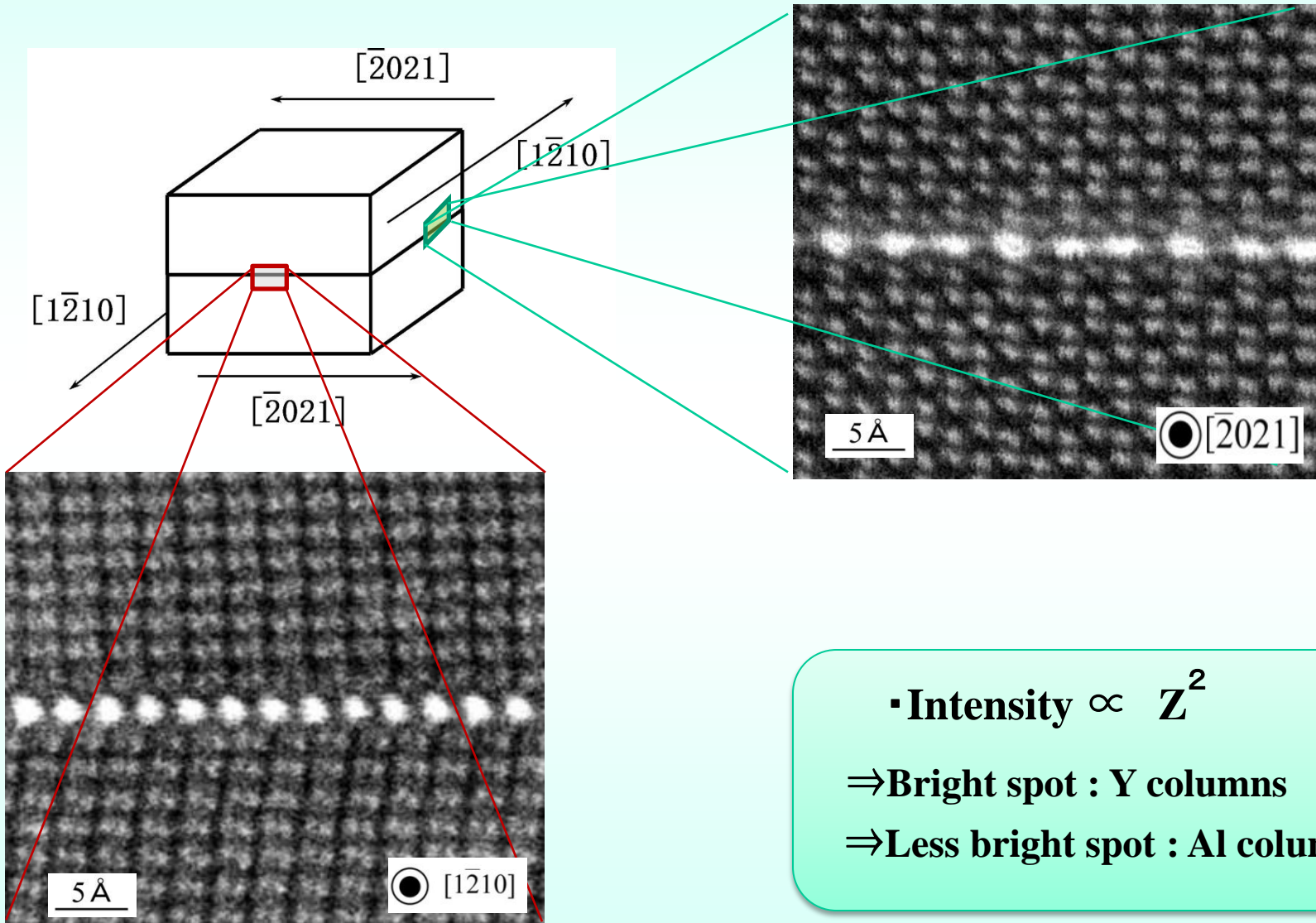
Science (2006)

Model for Creep Resistance Due to Doping



The presence of Y has been shown to increase the covalency (and strength of the cation-anion bonds) in alumina GB

HAADF-STEM images of Y doped $\Sigma 13$ grain boundary

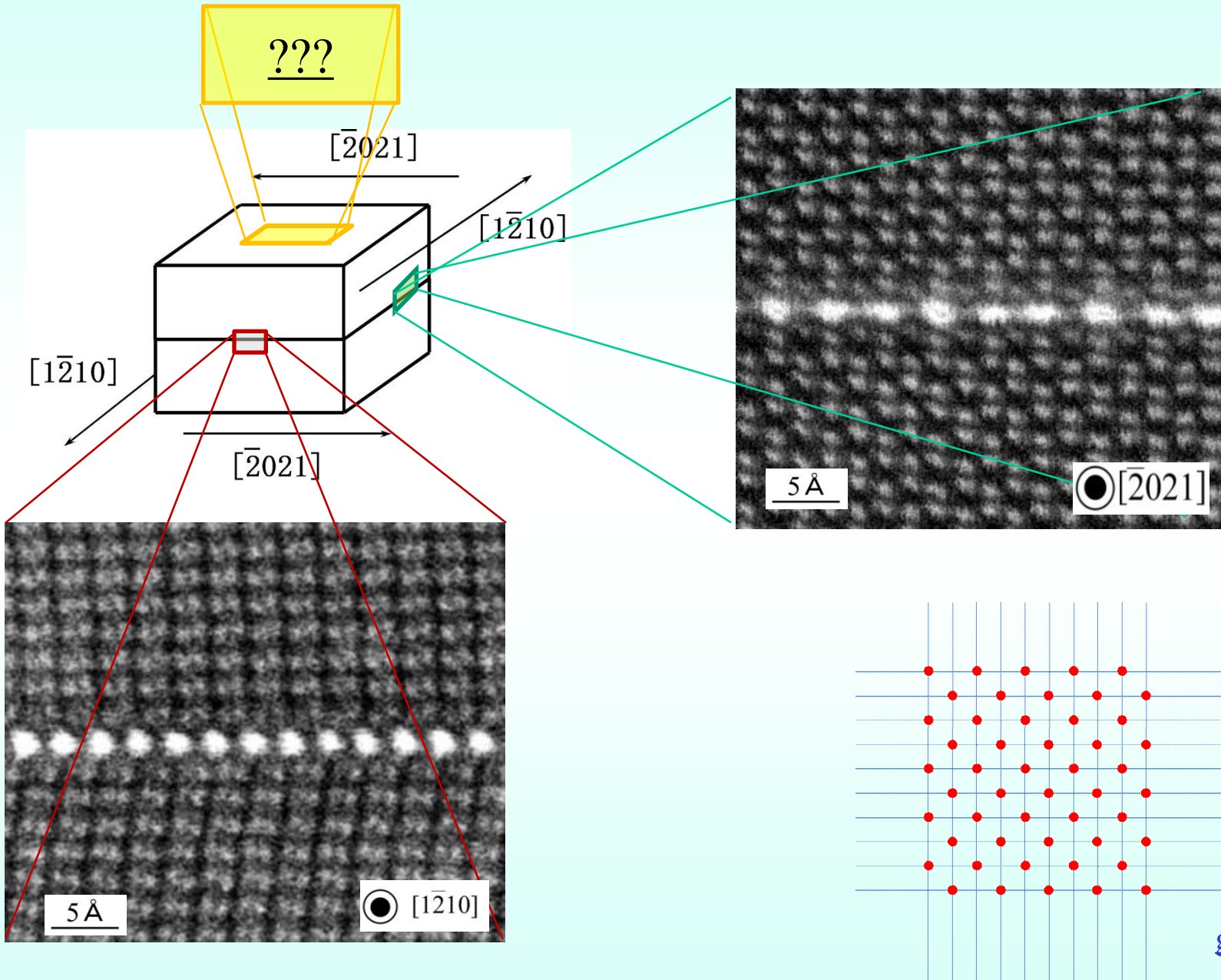


• Intensity $\propto Z^2$

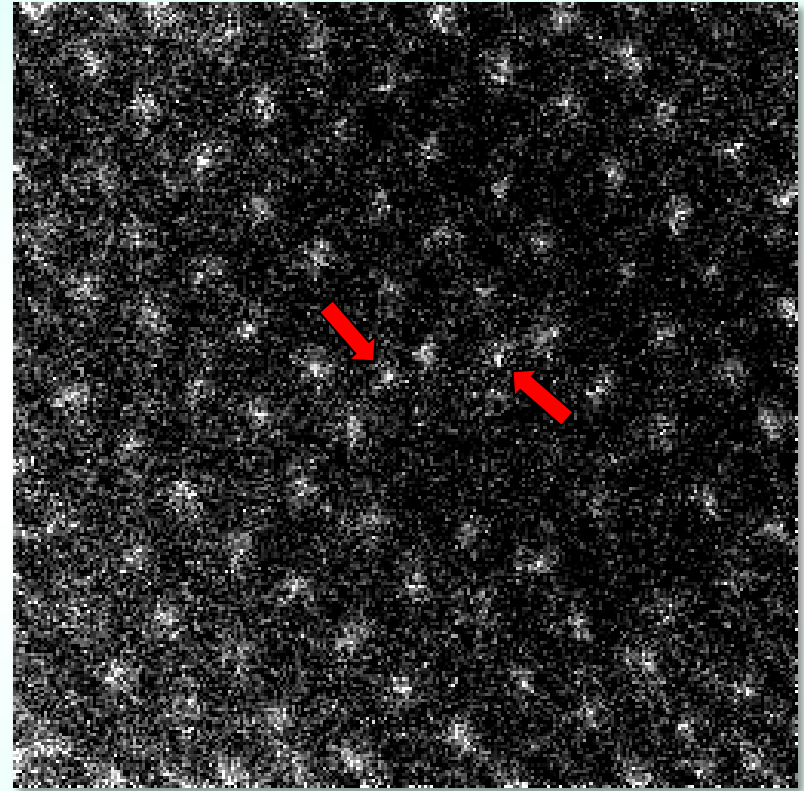
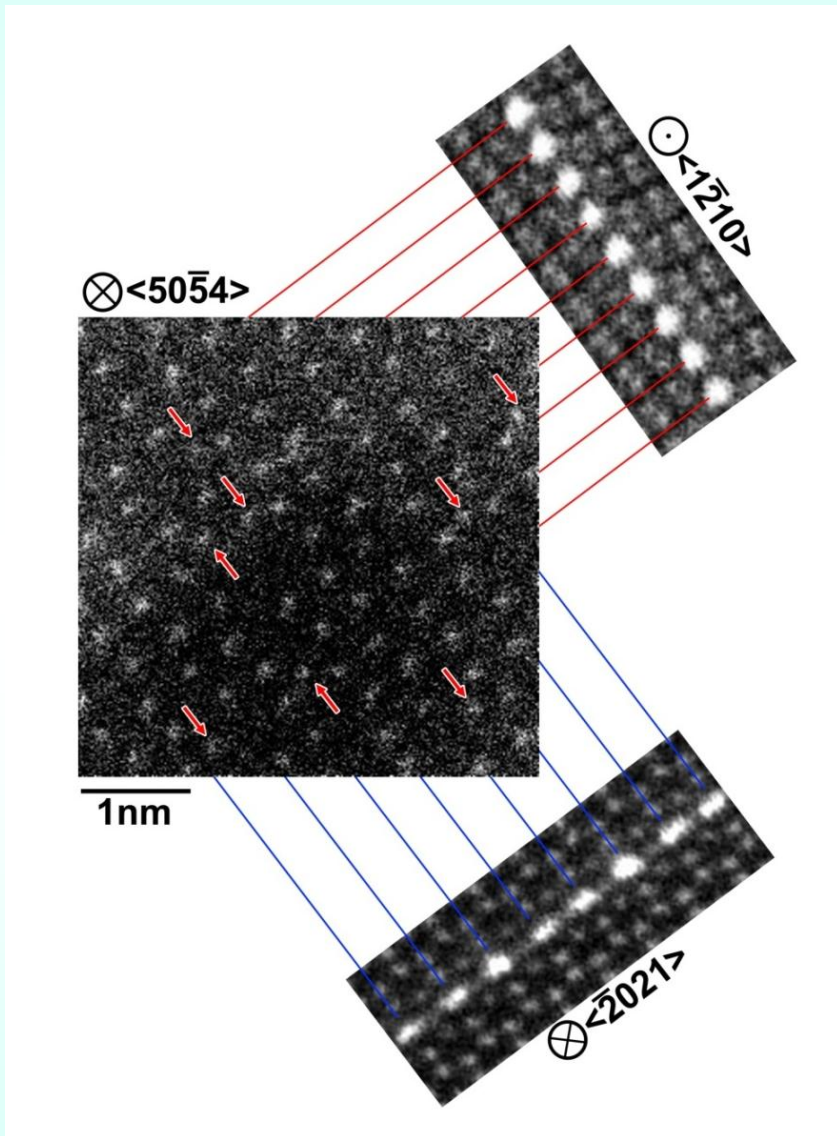
⇒ Bright spot : Y columns

⇒ Less bright spot : Al columns

Plan-view imaging



Local disordering at the interface!



Disordering at a single atom level can be detected!

STEM plan-view imaging directly highlights individual dopant atoms in a buried interface!

STEM-Theoretical Calculation-Materials Design

(1) Segregated Dopants at Ceramic Grain Boundaries

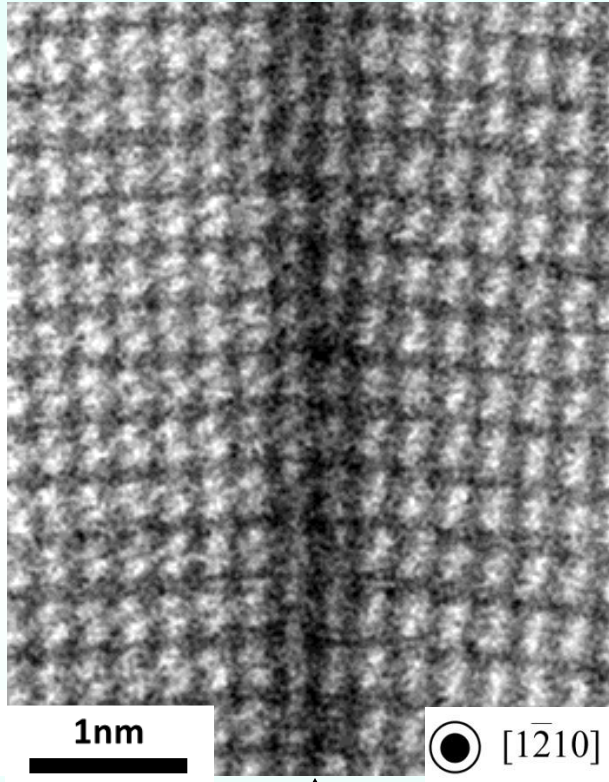
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- *Functional materials ($\text{ZnO} : \text{Pr}$)*

(2) Catalyst (Au-nanoparticle on TiO_2)

(3) STEM Annular Bright Field Imaging Direct Observation of Li Ions and H (LiMn_2O_4 , LiCoO_2 , VH_2)

Al₂O₃: Ca-doped G.B.(Σ13)

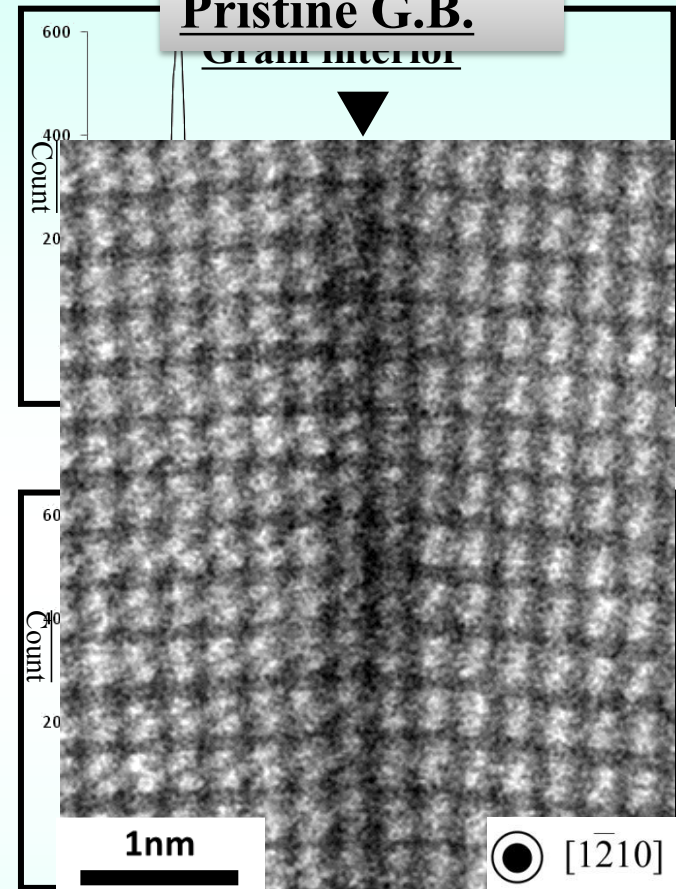
Ca-doped G.B.



G.B.

Bright spots were not observed

Pristine G.B.



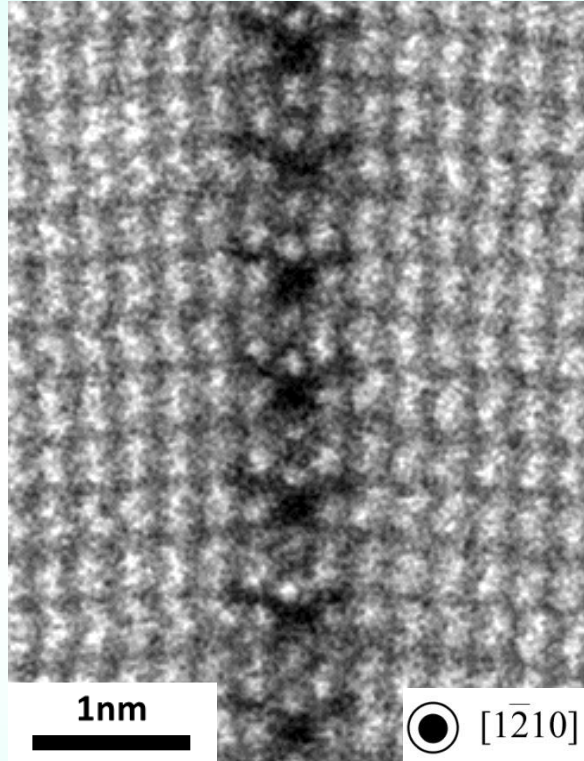
G.B.

Ca atoms were not detected

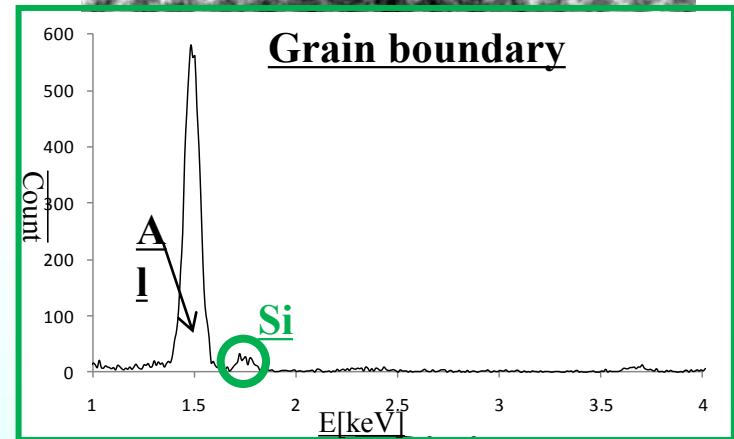
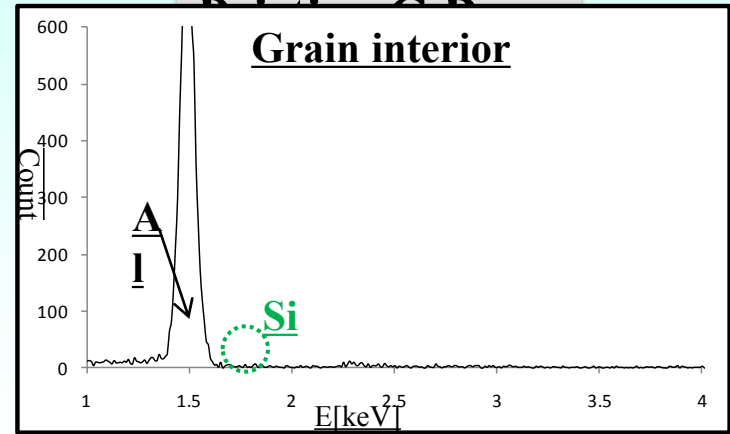
Ca(Z=20) >> Al(Z=13) >> O(Z=8)

Al₂O₃: Si-doped G.B.

Si-doped G.B.



G.B.



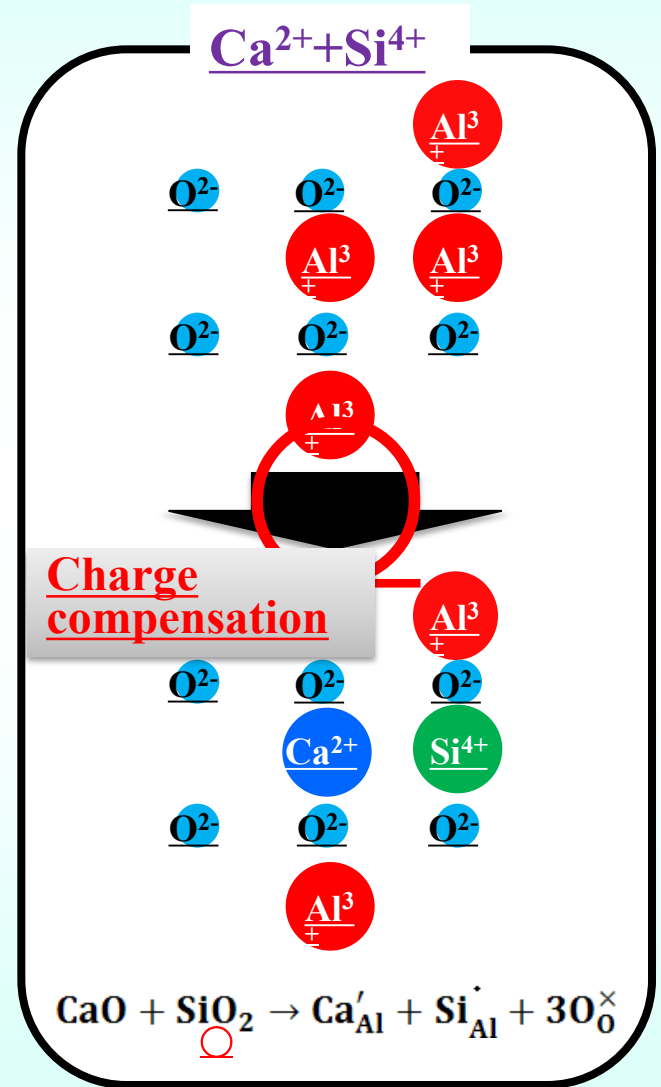
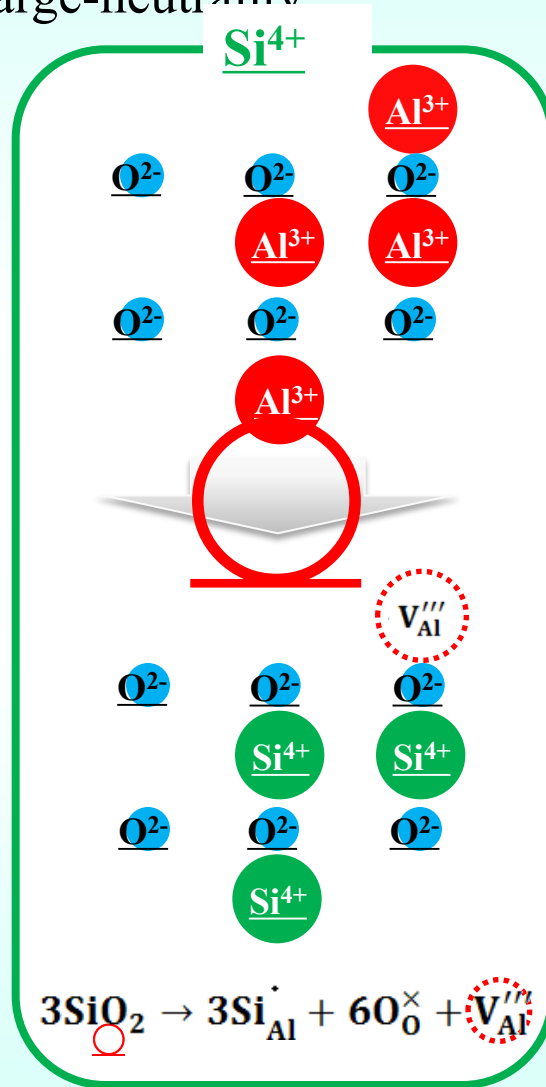
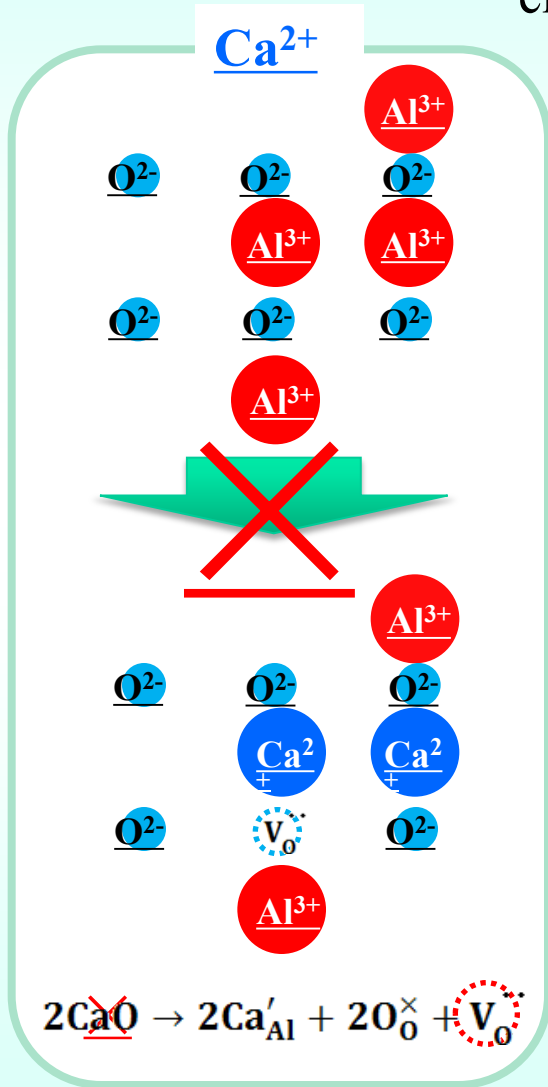
Different from pristine G.B.

Si atoms were detected



Charge Effect

To segregate $\text{Ca}^{2+}/\text{Si}^{4+}$ and keep charge-neutrality



STEM-Theoretical Calculation-Materials Design

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Varistor (ZnO)

Device to protect from static electricity and mechanical shock

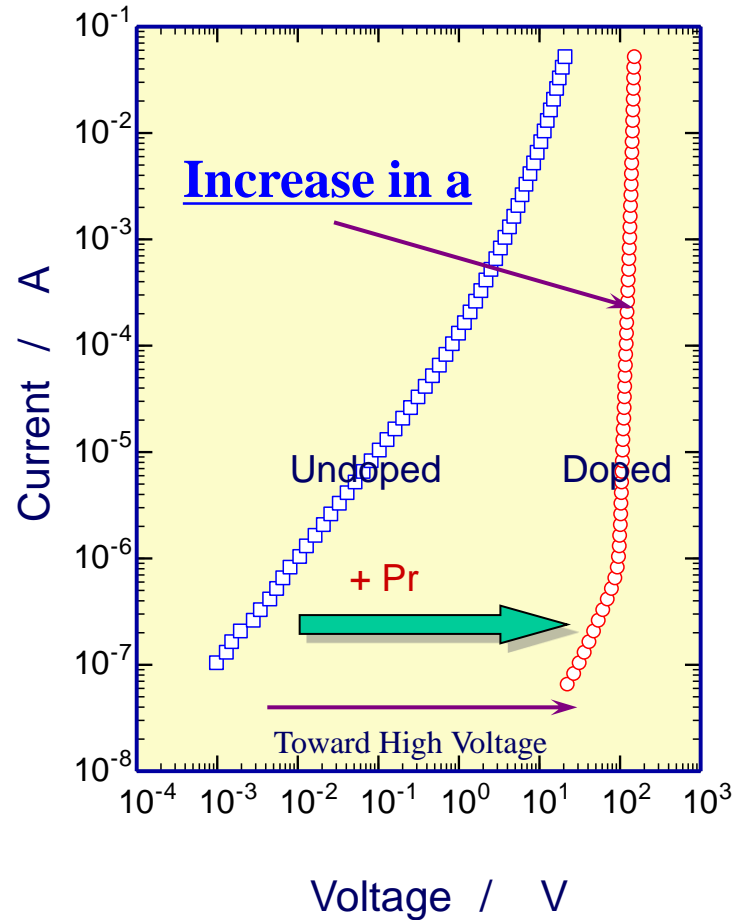


Protection device

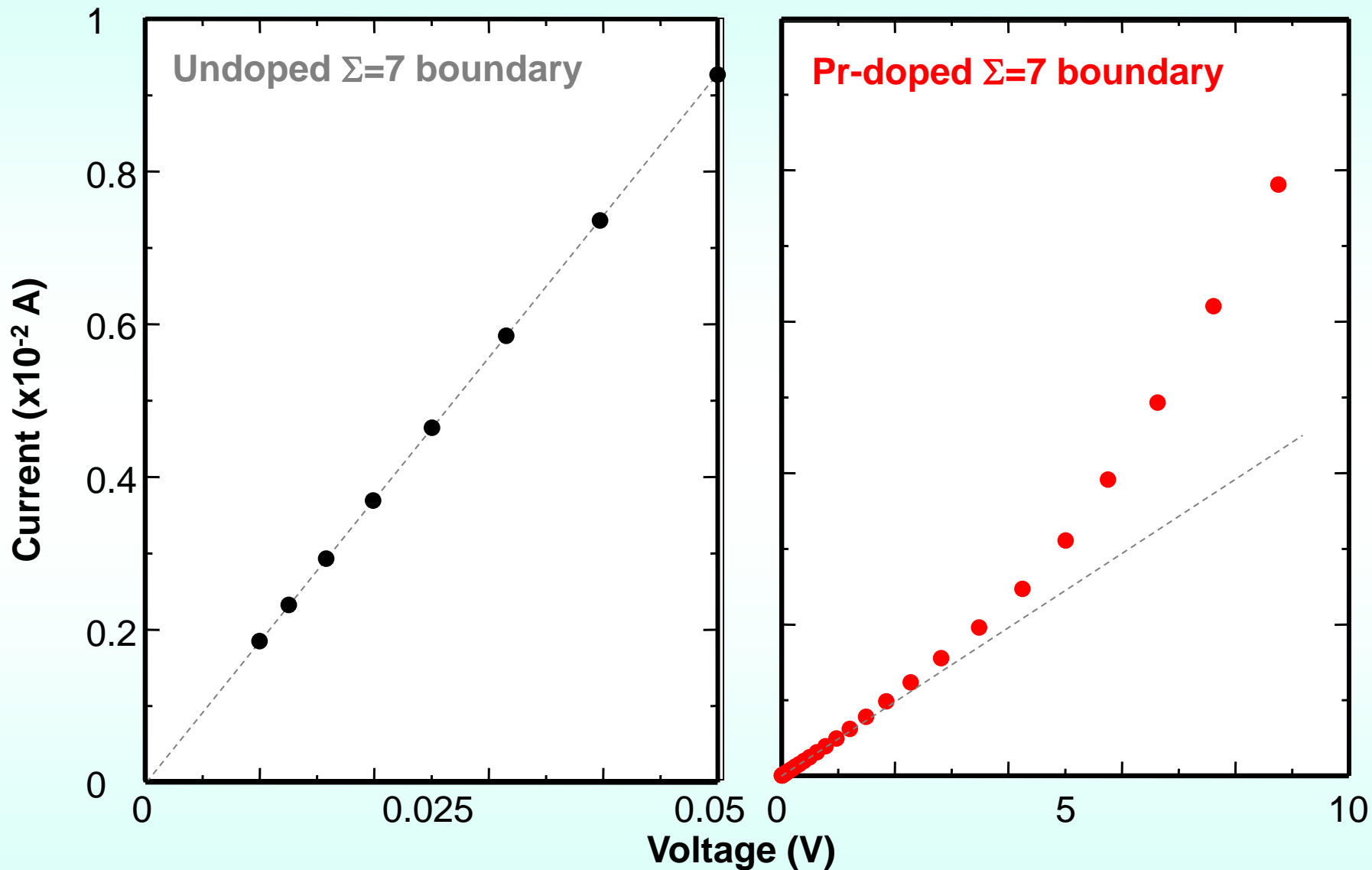
$\sim 0.2\text{mol\%}-\text{Pr}$ doping



Great Improvement of Varistor Properties

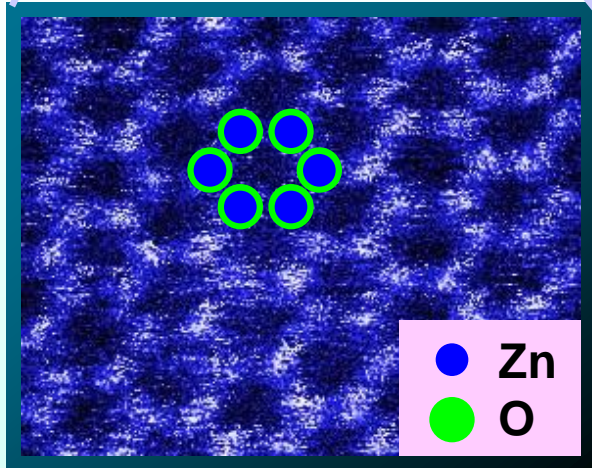
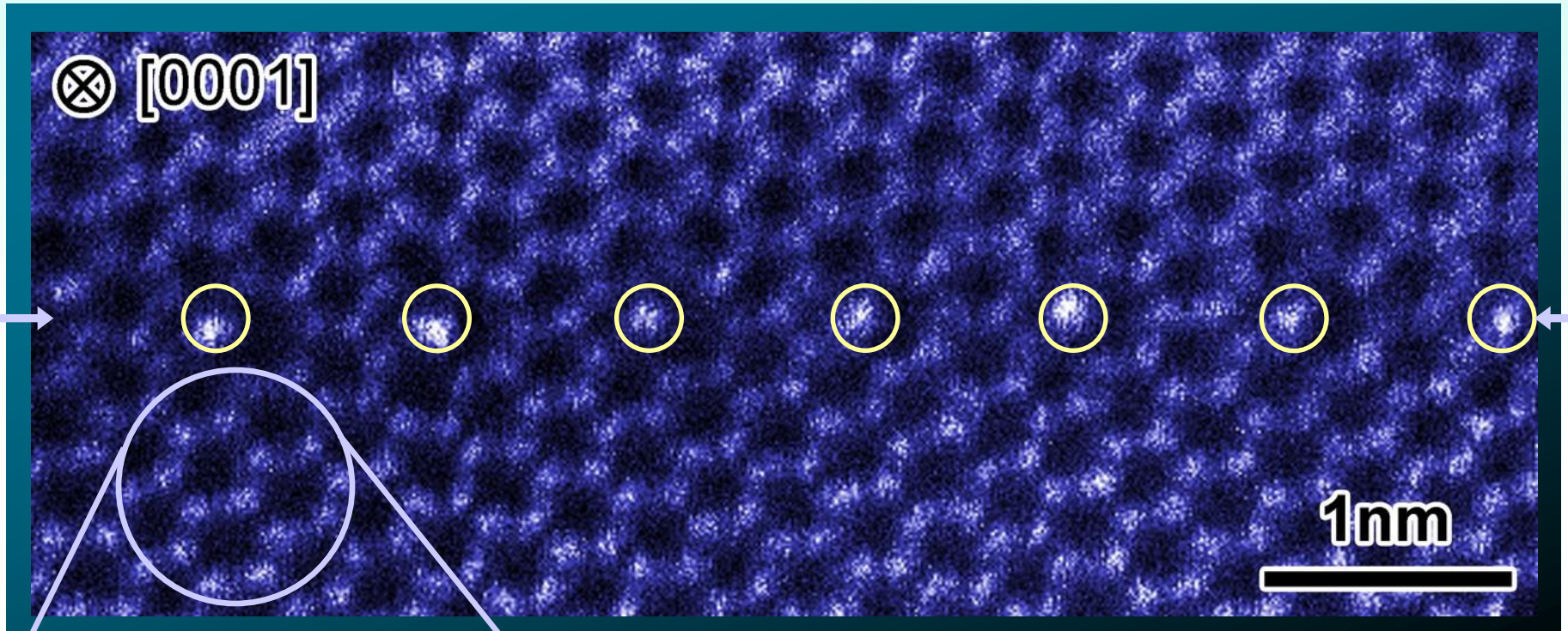


I-V characteristic of ZnO bicrystals



The nonlinear *I-V* characteristic results from the Pr.

HAADF-STEM image of the Pr-doped ZnO GB



- **Z-contrast imaging**

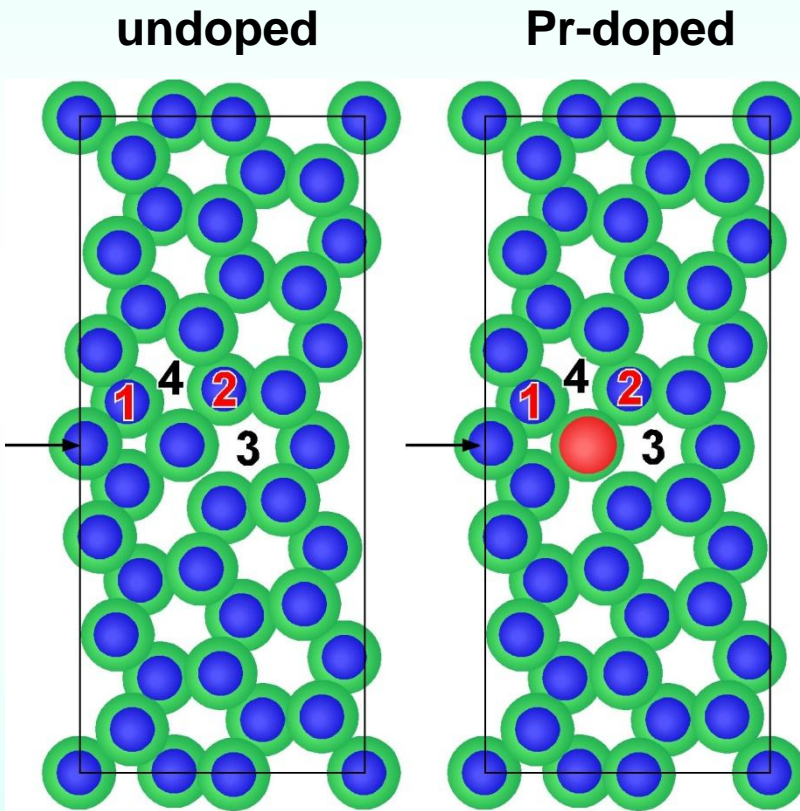
Heavier atoms (Pr: $Z=59$, cf. $Z=30$ for Zn) appear much brighter.

→ **The Pr segregates to specific atomic columns of the boundary (no interfacial layers).**

PRL (2006)

Formation energy of Zn vacancy (V_{Zn}) and O interstitial (O_i)

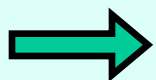
V_{Zn} at the site 1 and 2, O_i at 3 and 4 are calculated.



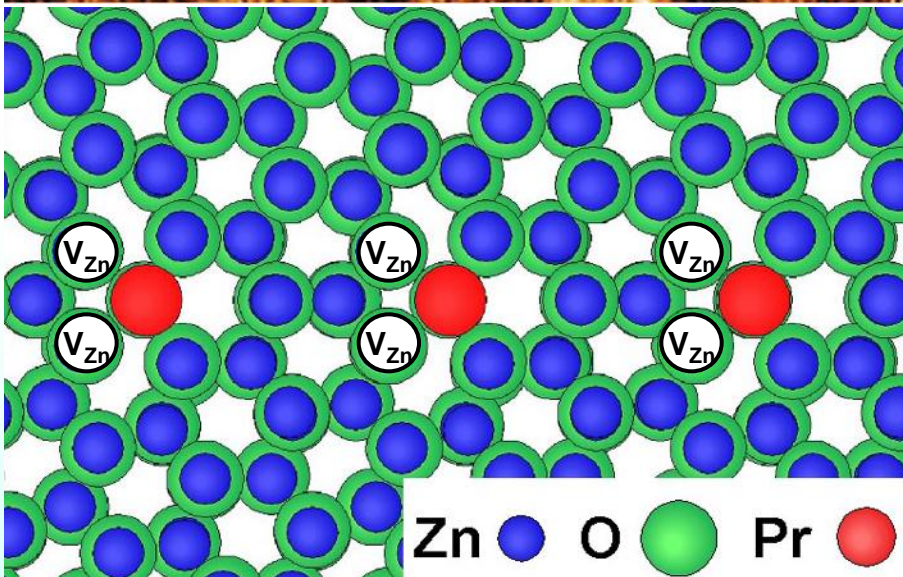
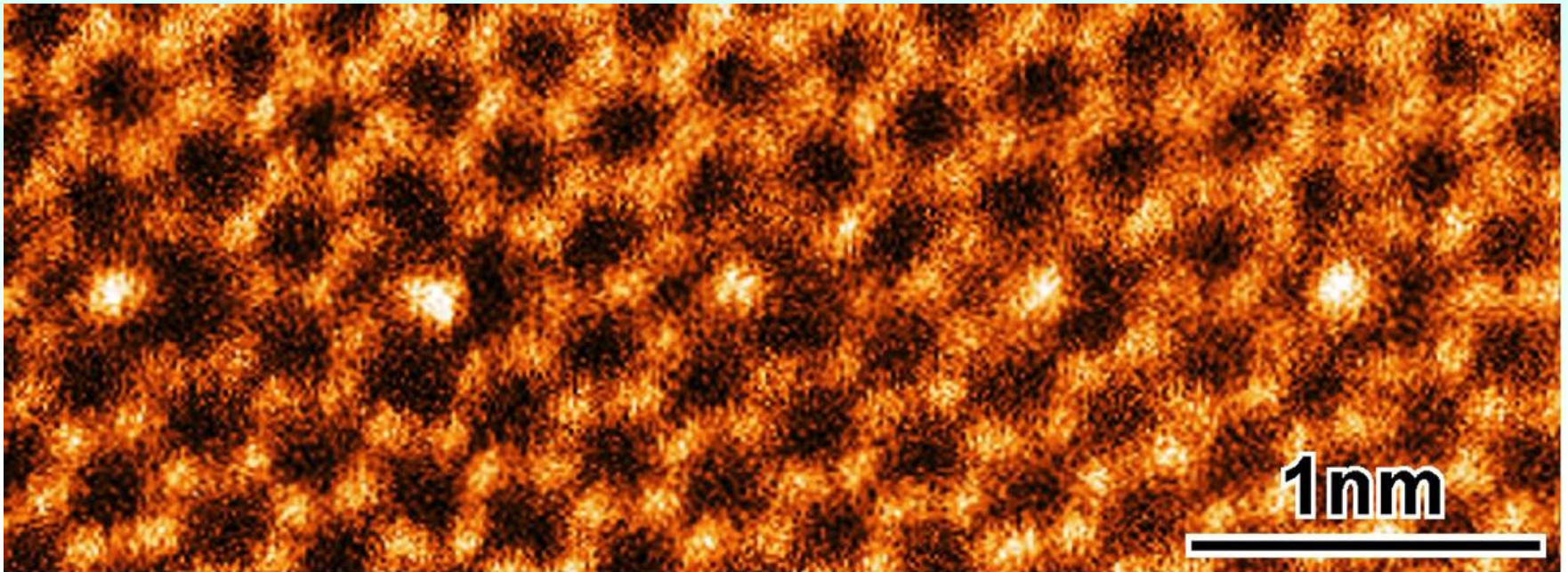
Defect formation energy

undoped (eV)		Pr-doped (eV)
0.4	1 (V_{Zn})	0.1
1.4	2 (V_{Zn})	0.7
3.2	3 (O_i)	1.5
3.2	4 (O_i)	2.2

V_{Zn} is more stable than O_i .
Pr-doping lowers the formation energies.



Pr promotes the formation of native defects. (particularly V_{Zn})



The role of Pr can be understood by First Principles calculation

STEM+First Principle



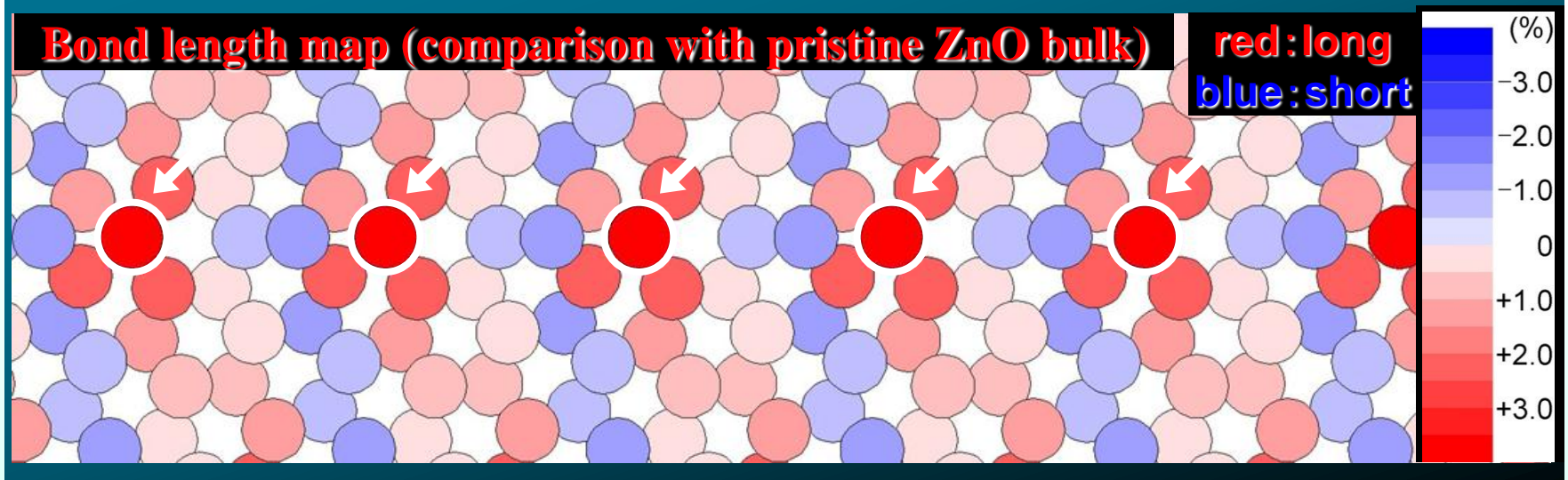
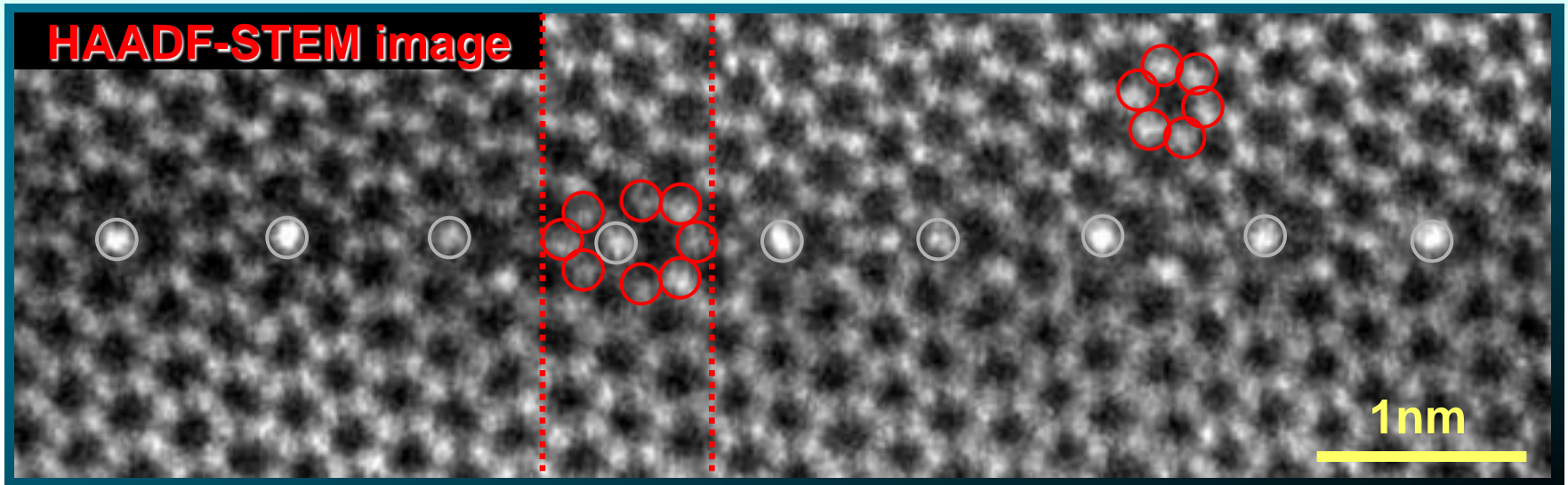
Origin of Varistor Properties



High Performance Varistor

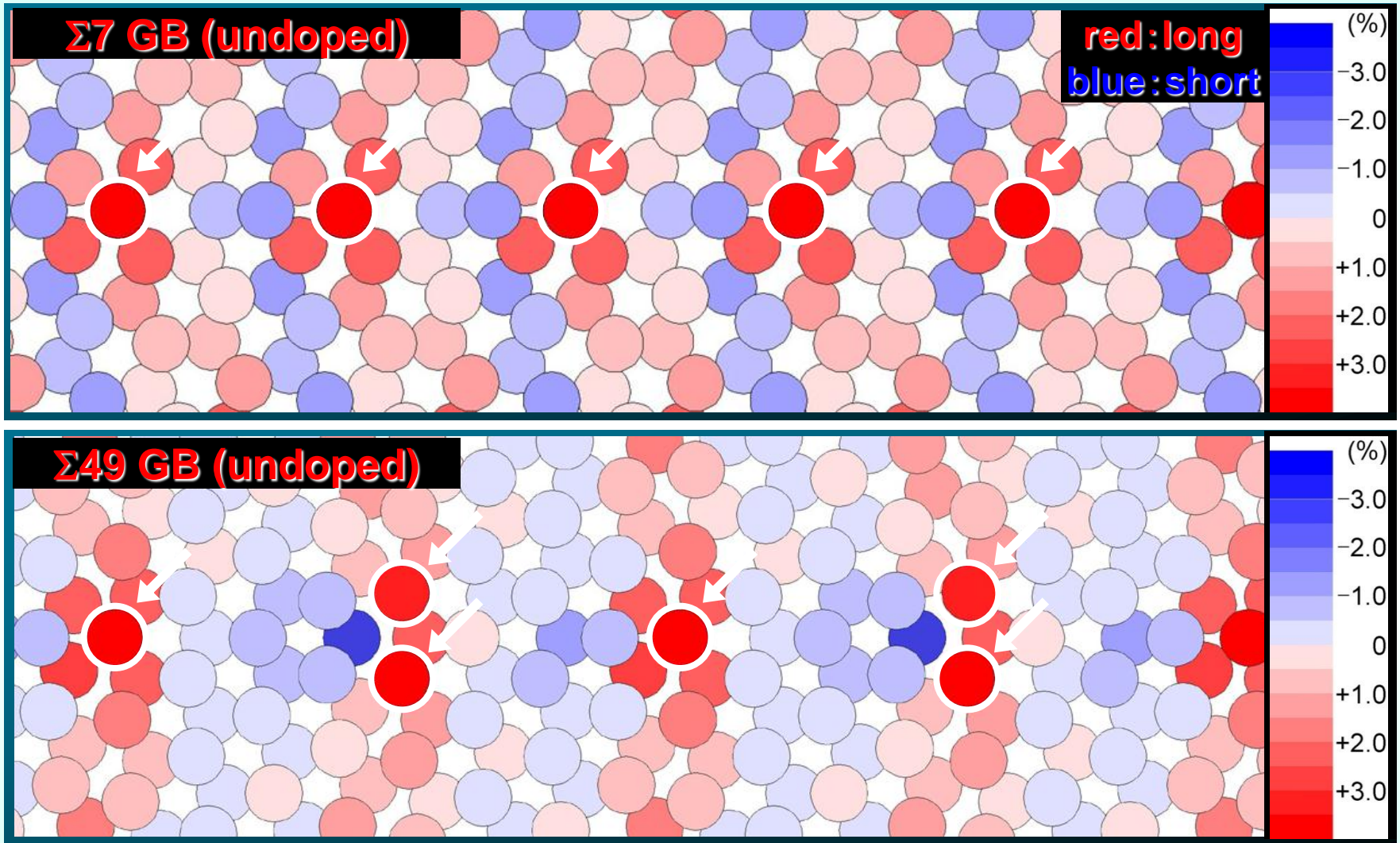
PRL (2006)

Factor to determine the segregation site; Pr-doped ZnO $\Sigma 7$ GB

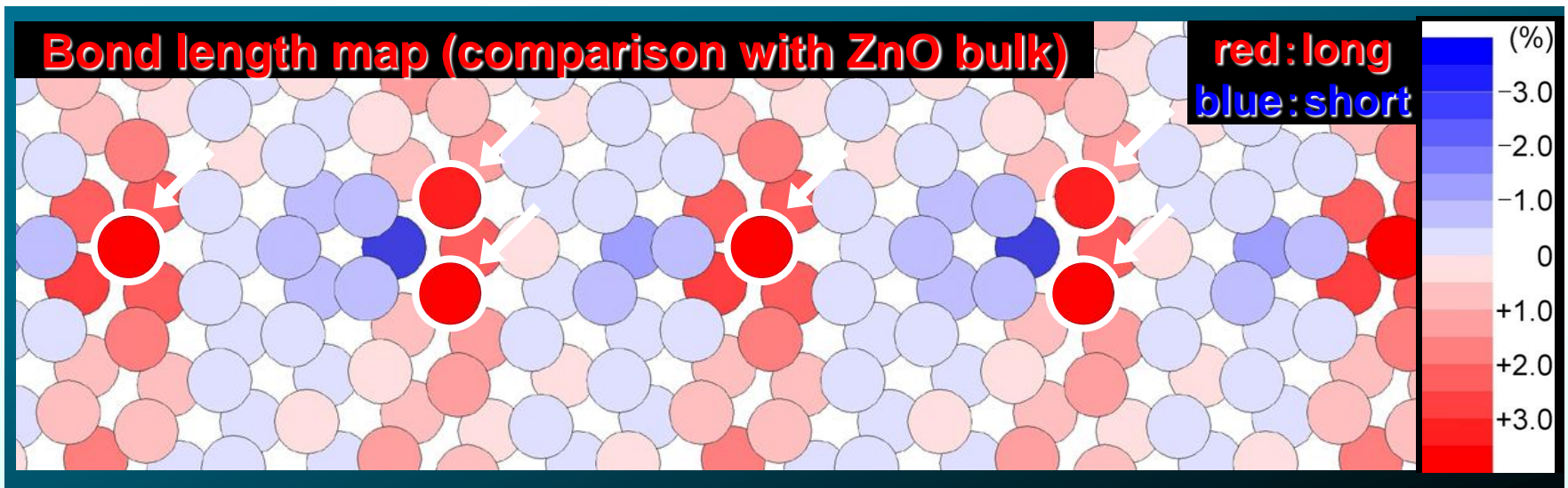
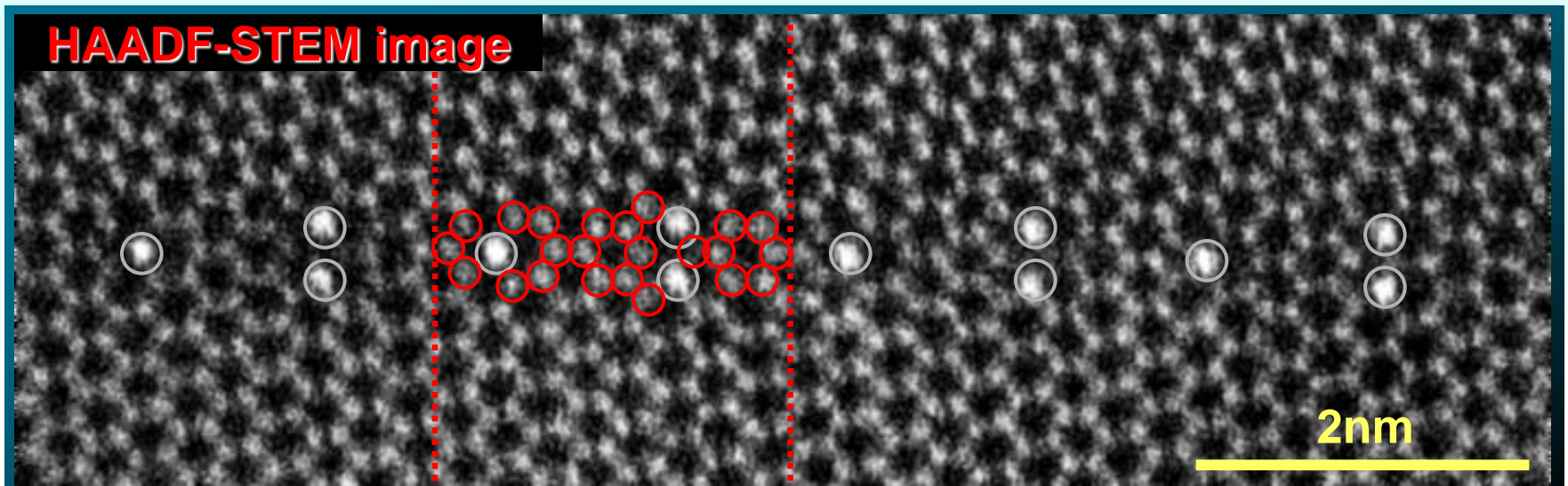


Pr segregates at the sites of the locally longest inter-atomic distance.

Bond length map (comparison with ZnO bulk)



Pr segregates to the sites of locally largest inter-atomic distance.



Pr segregates at the sites of the locally longest inter-atomic distance.

PRB (2010)

STEM-Theoretical Calculation-Materials Design

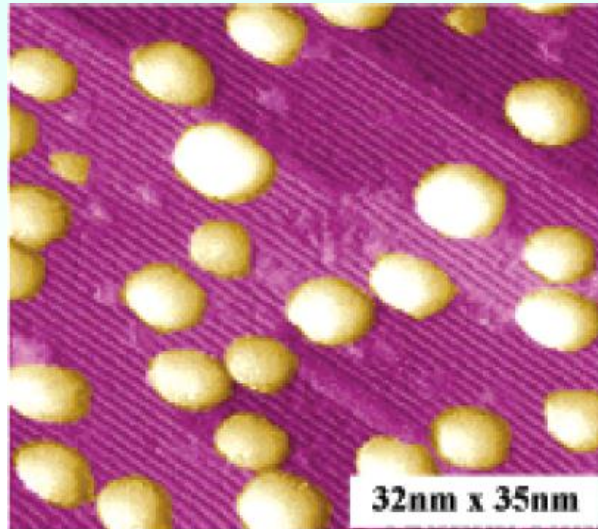
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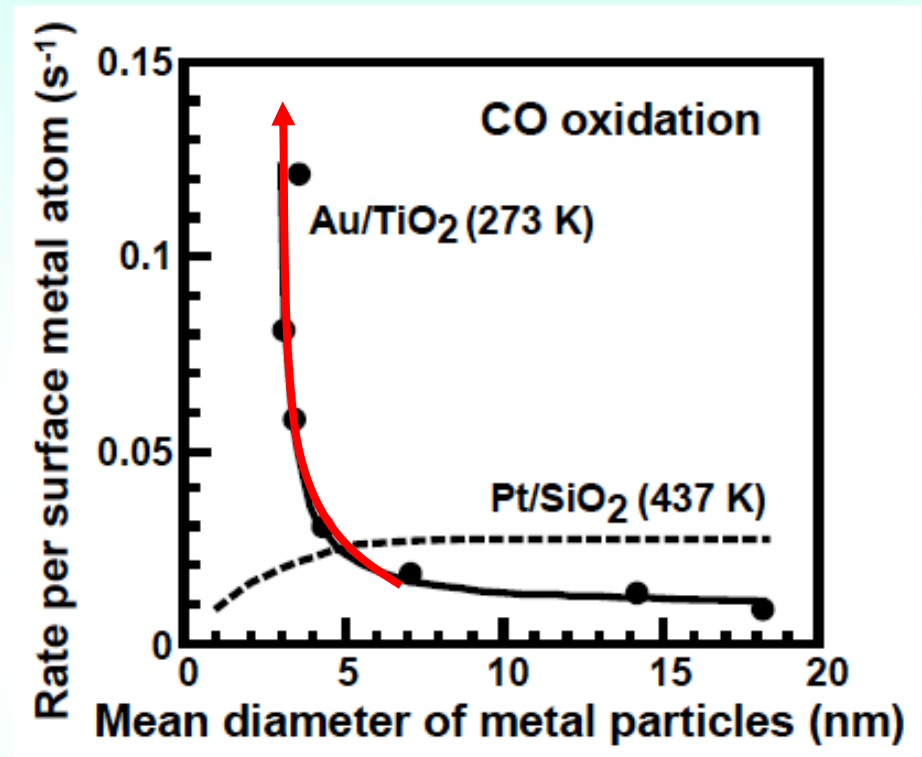
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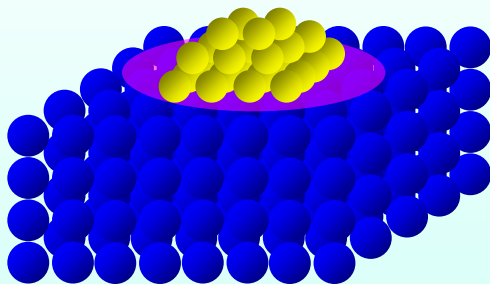
Nano hetero interface — Nanosized Au particles on TiO₂



STM image of Au nanoparticles on TiO₂ surface
M. Valden, X. Lai and D.W. Goodman, Science (1998)

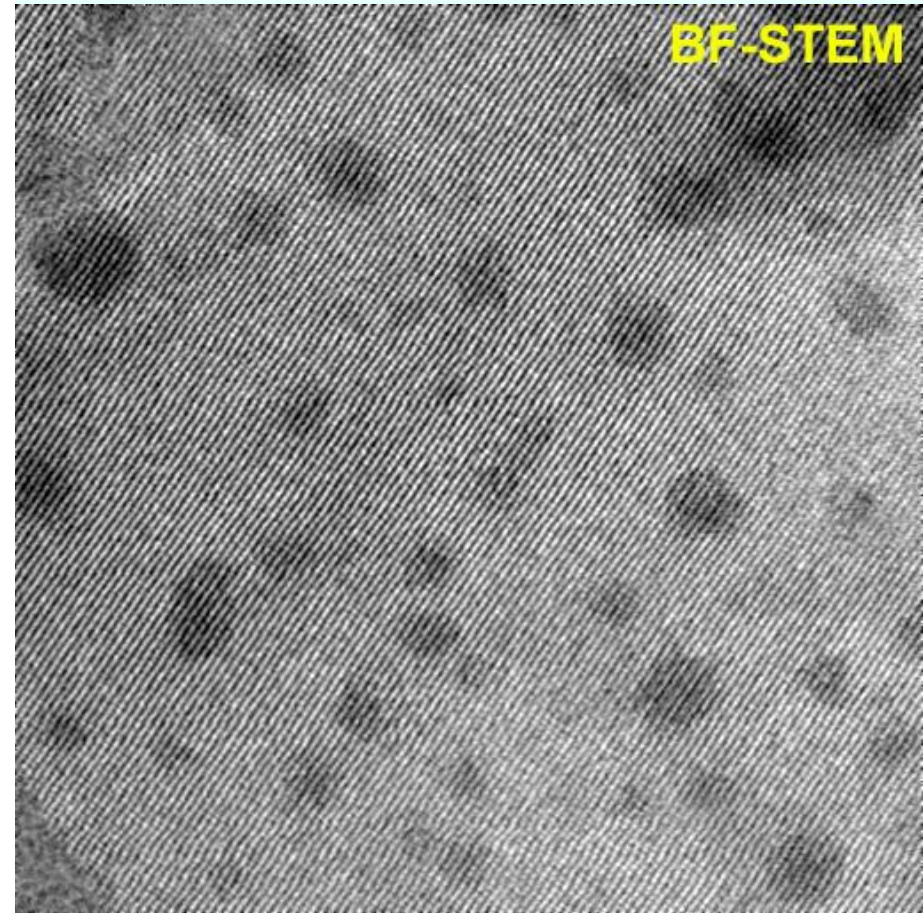
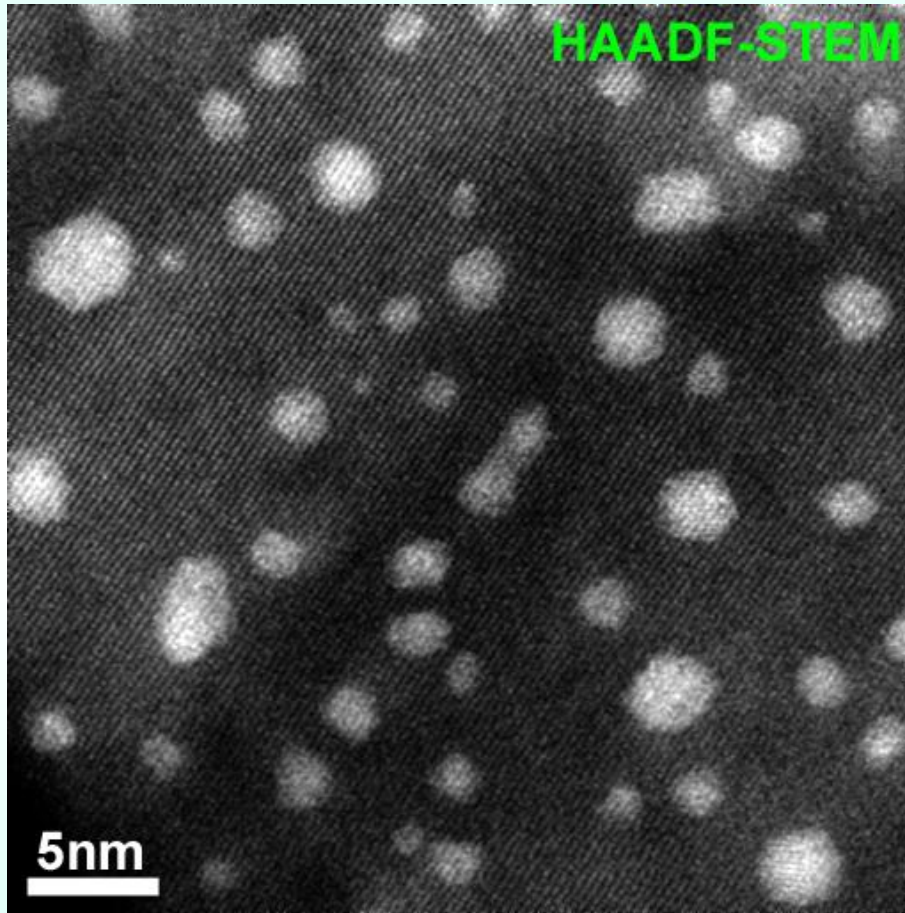


Au size effect on CO oxidation
M. Haruta et al., J. Catal. (1993)



“Interfacial interaction” at nano-scale hetero interface is a key factor!

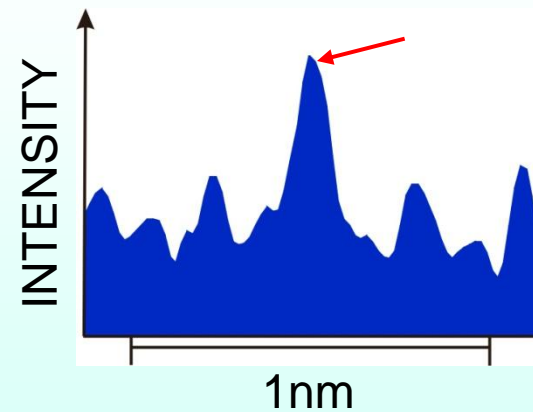
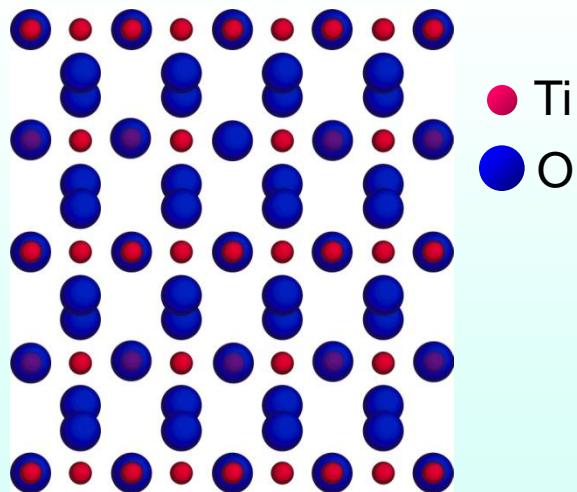
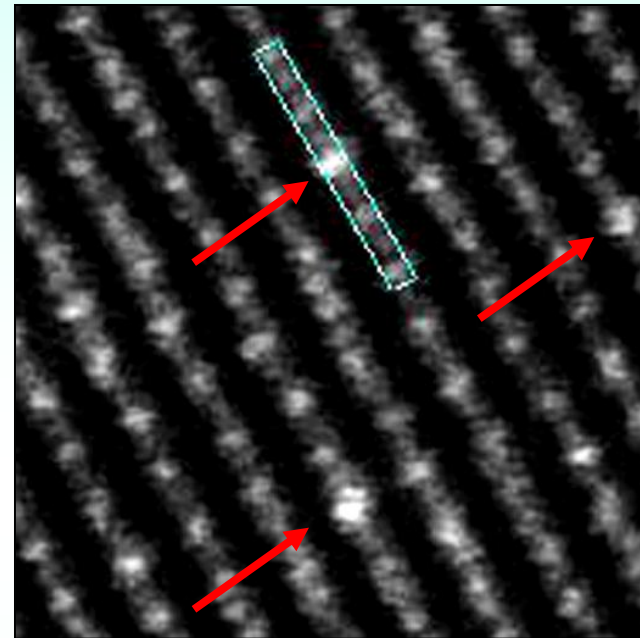
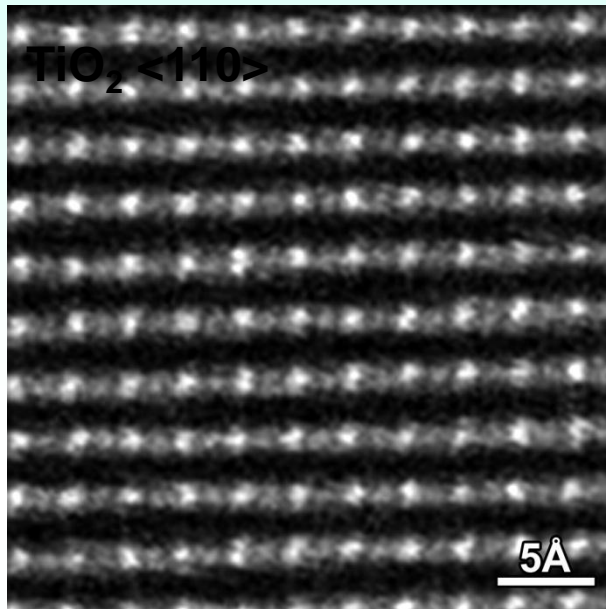
Comparison between HAADF-STEM and BF-STEM images of Au nanoparticles on TiO₂



Heavy Au particles can be clearly imaged by Z-contrast STEM !

Au single atoms on TiO₂ (110) surface

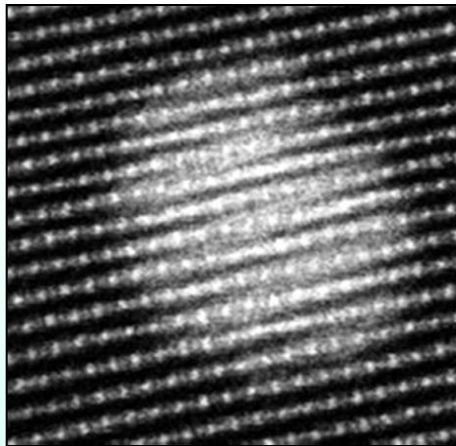
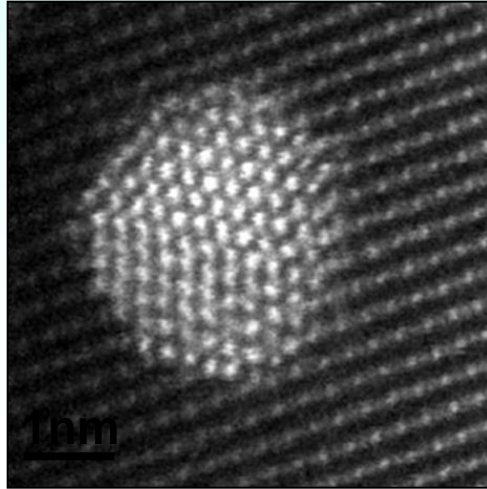
Au attached on Ti-O columns



Au single atoms attached to the specific surface sites

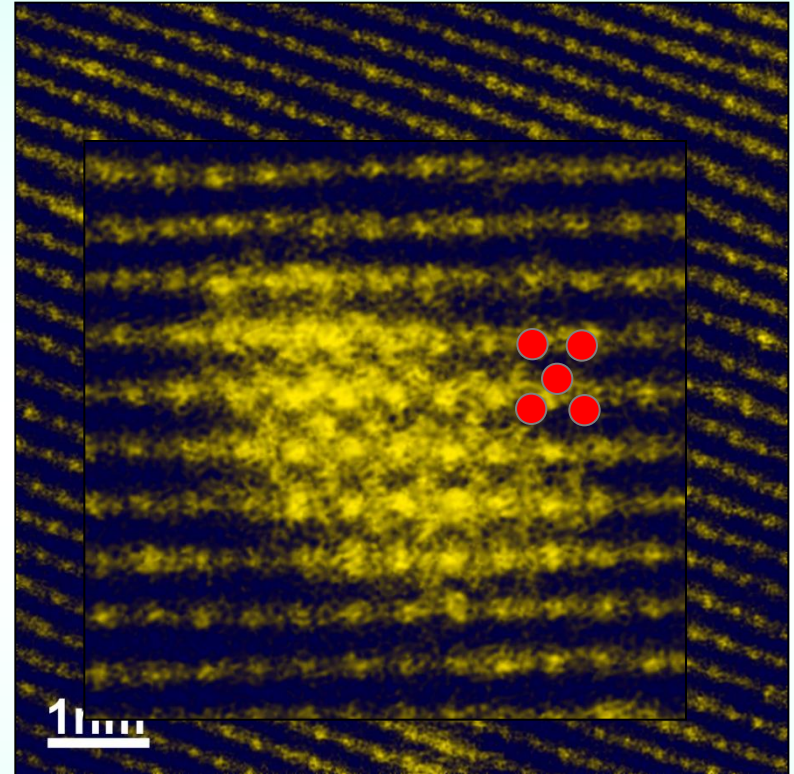
Au-TiO₂ crystal orientation and interface structures [PRL\(2007\)](#)

Au size >3nm



Au and TiO₂ have no lattice coherency

Au size <3nm

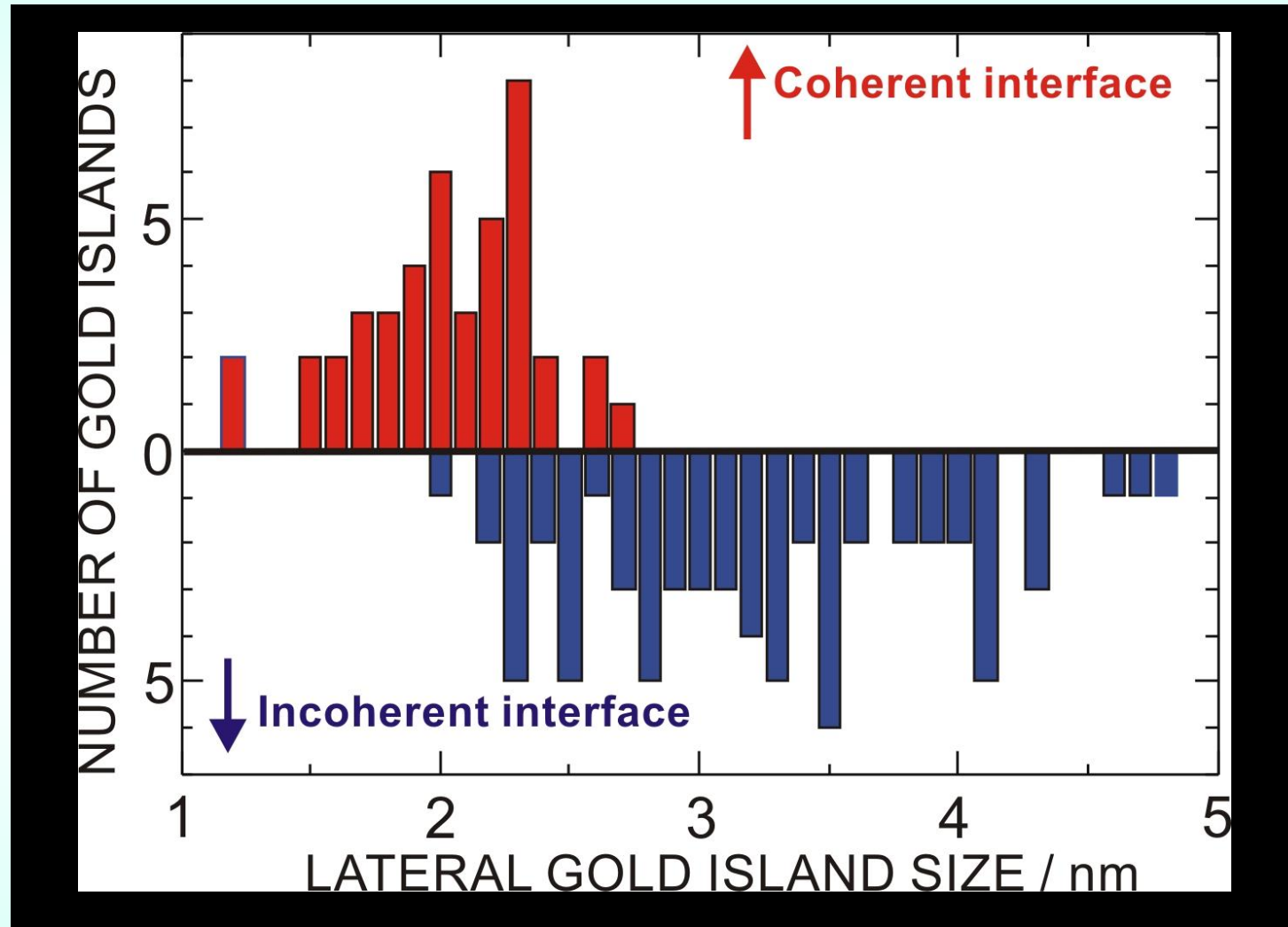


Unique epitaxial Au structure on TiO₂ surface



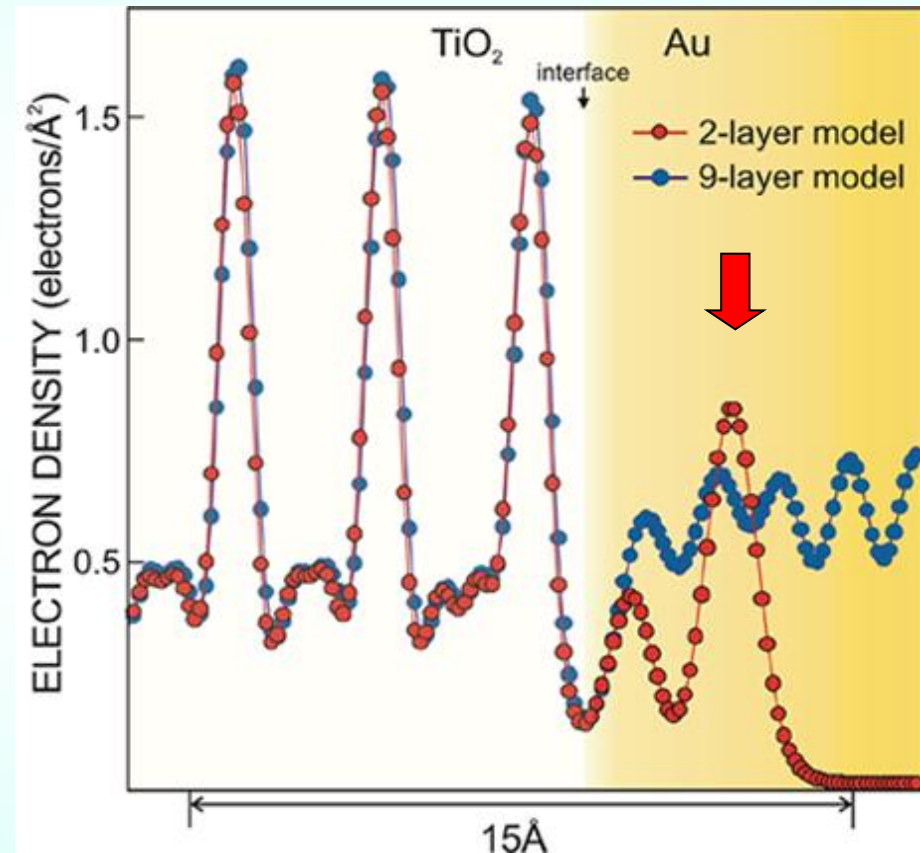
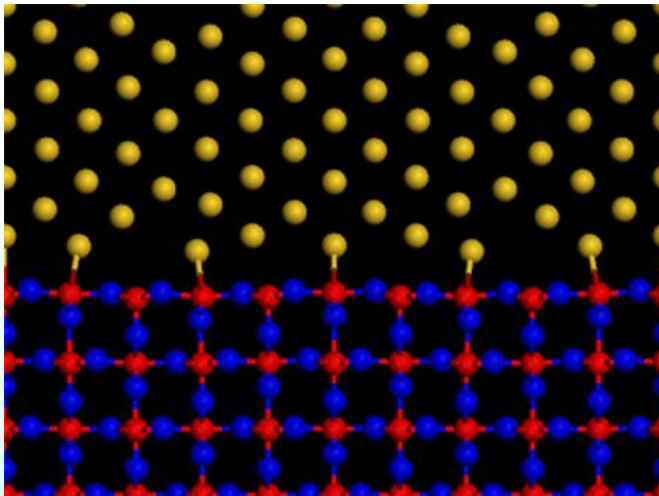
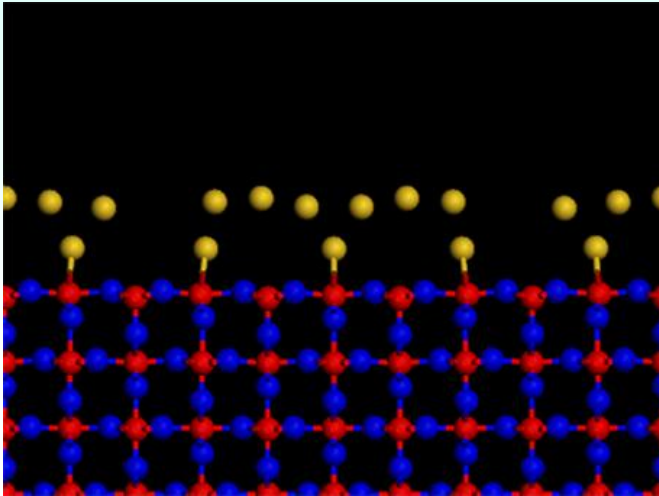
Nano-coherent interface between Au and TiO₂

Size dependent “coherent↔incoherent” interface transition



Au-TiO₂ interface structures dramatically change according to the Au sizes!

Electronic structures of Au nanoislands on TiO₂



When Au nanoislands are very small, TiO₂ substrate drastically changes their atomic as well as electronic structures through unique interface structures!

Short Break !

Gallery (Another Example (HAADF-STEM))

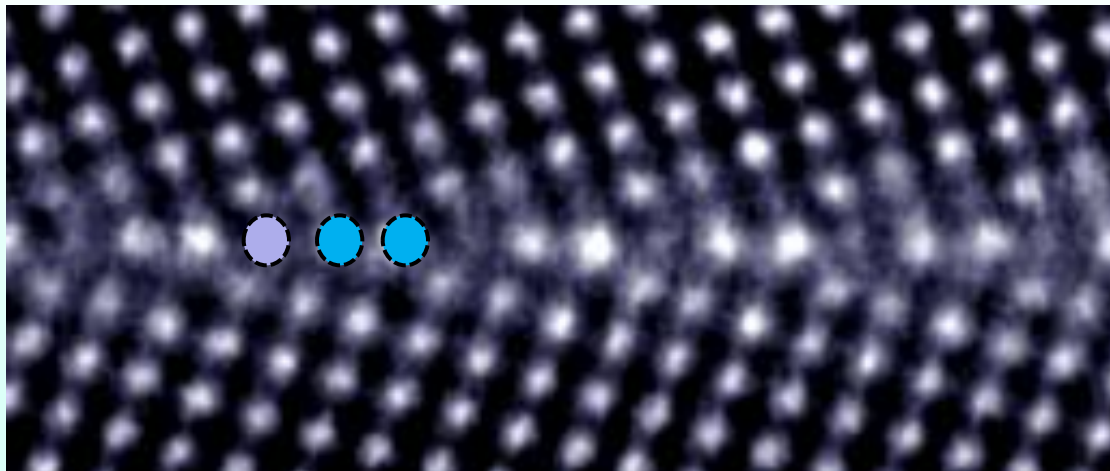
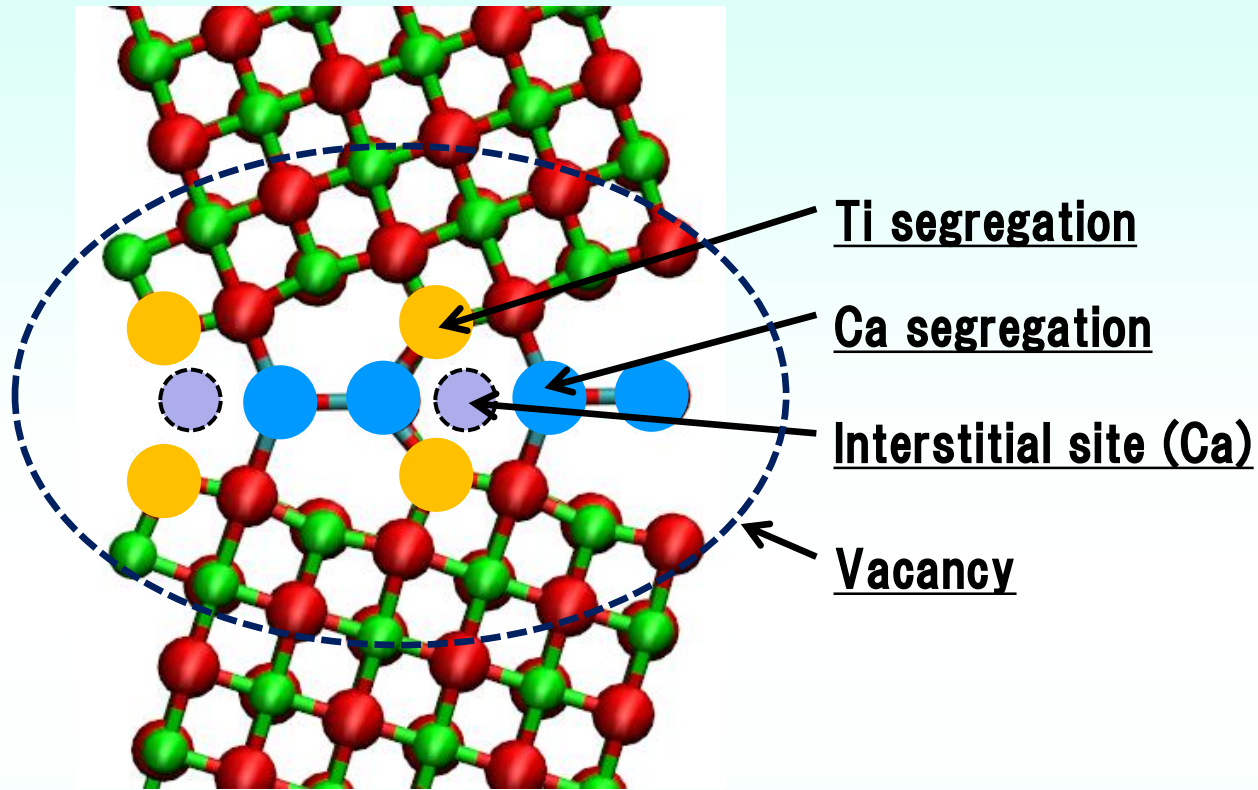
How STEM is powerful to reveal the nature of materials!

Ca²⁺Ti⁴⁺doped MgO

Ce doped c-BN

Eu doped Al₂O₃ (Dislocation)

Ca²⁺+Ti³⁺ co-doped GB (MgO Σ5GB)

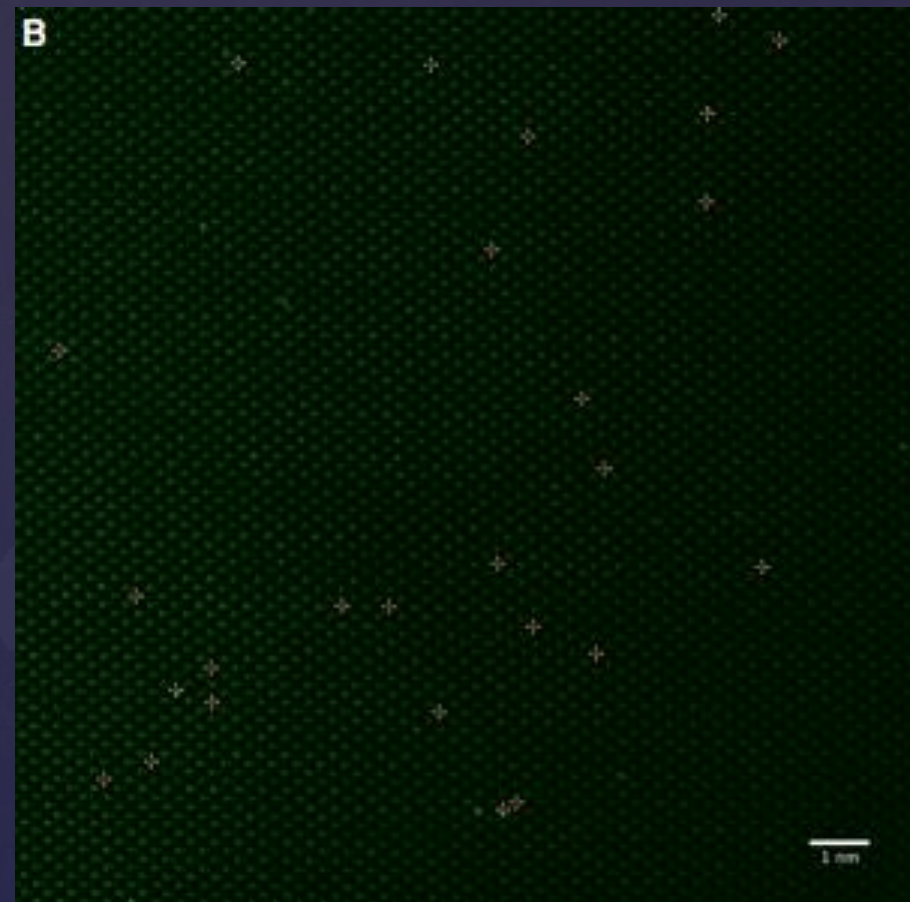
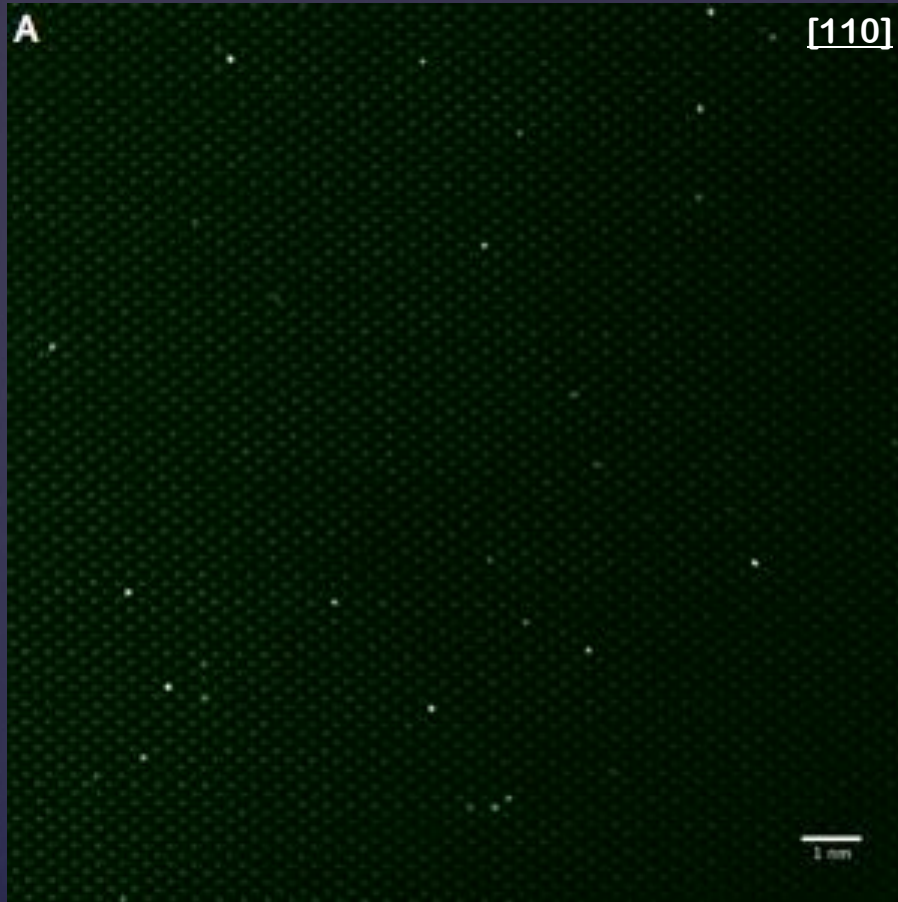


*GB Ordered Segregation
Superstructures*

Nature (2011)

Single Atom Imaging in a crystal

Spatial distribution of Ce atoms in c-BN (Solid Solution)

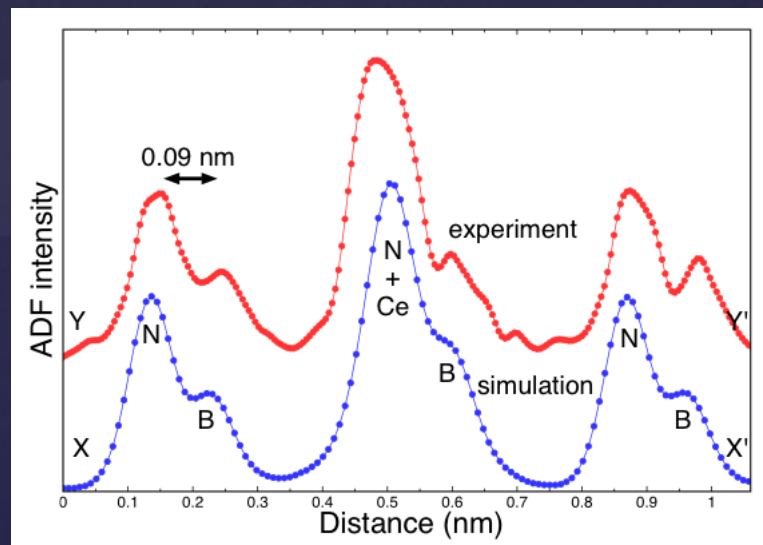
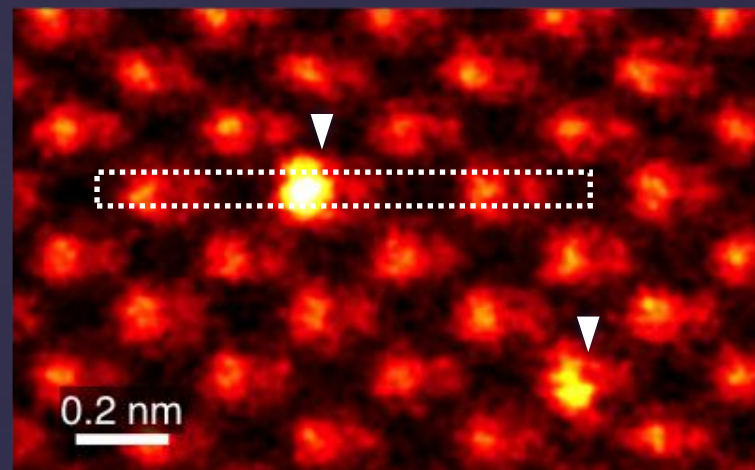
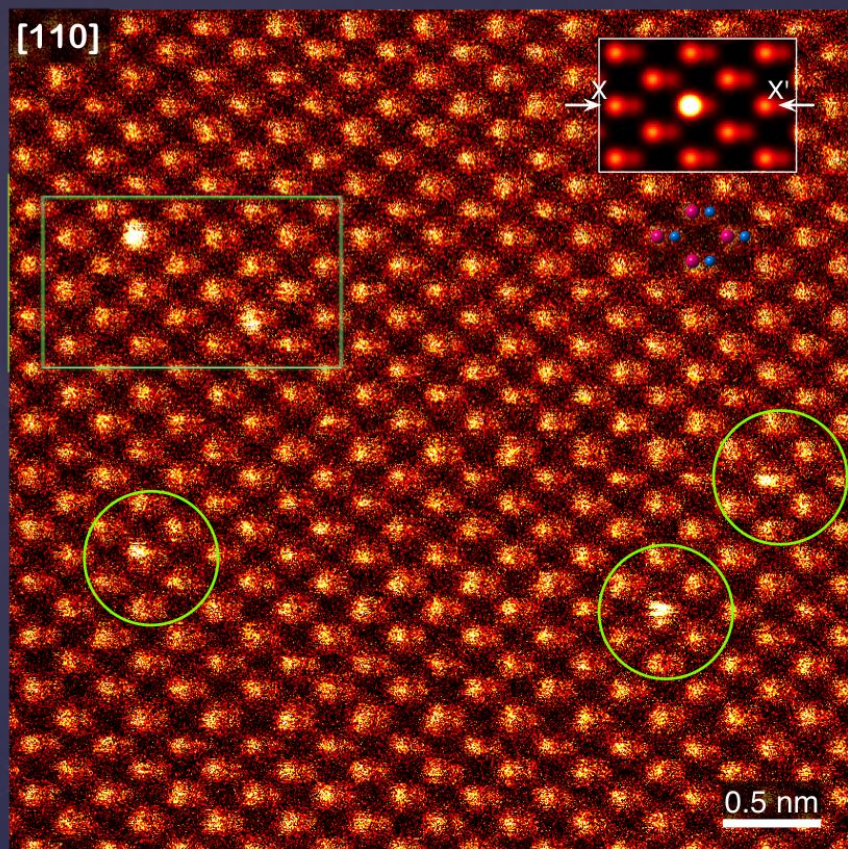


ZB = 5, ZN = 7, ZCe = 58

- Ce distribute as “isolated” single atoms
- brightness: depth or overlap

- thickness measurement: EELS
- atom counting by local maxima
- < 20 nm, ignoring overlap

Atomic site of single Ce atoms in ADF STEM



~8 pA, 200 kV BN-dumbbell: ~0.9 Å

Ce occupies N-antisite (cation-anion substitution) PRL(2013)

Short Break

Great Breakthrough in Materials Science!

Ca²⁺Ti⁴⁺doped MgO

Complicated GB segregation

Ce doped c-BN

Solid solution

Eu doped Al₂O₃ (Dislocation)

Cottrell atmosphere

STEM-Theoretical Calculation-Materials Design

(1) Segregated Dopants at Ceramic Grain Boundaries

- *Single dopant ($\text{Al}_2\text{O}_3 : \text{Y}^{3+}$)*
- *Co-dopant ($\text{Al}_2\text{O}_3 : \text{Ca}^{2++}\text{Si}^{4+}$)*
- *Functional materials ($\text{ZnO} : \text{Pr}$)*

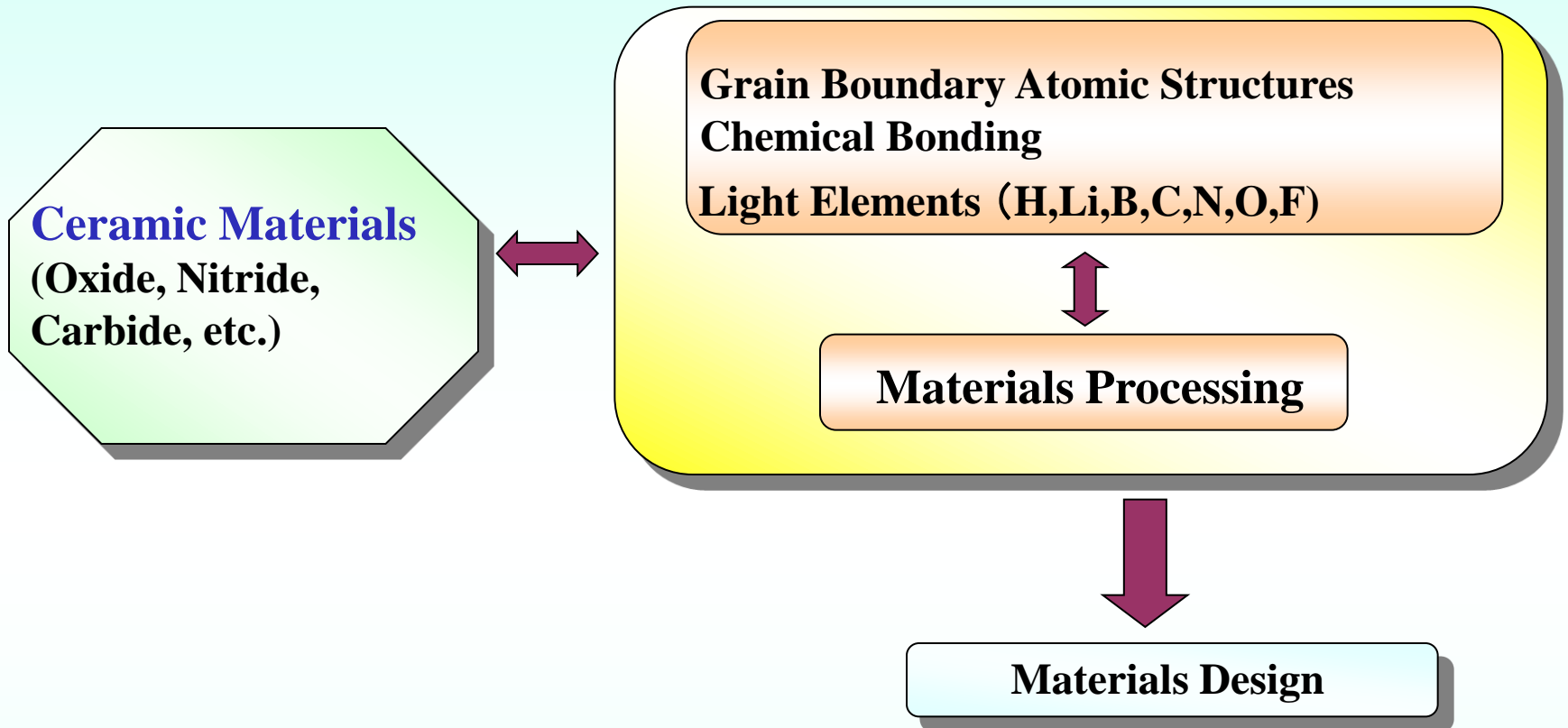
(2) Catalyst (Au-nanoparticle on TiO_2)

(3) STEM Annular Bright Field Imaging

Direct Observation of Li Ions and H

(LiMn_2O_4 , LiCoO_2 , VH_2)

Background



New Approach

- Visualization of Light Elements (Direct Observation)

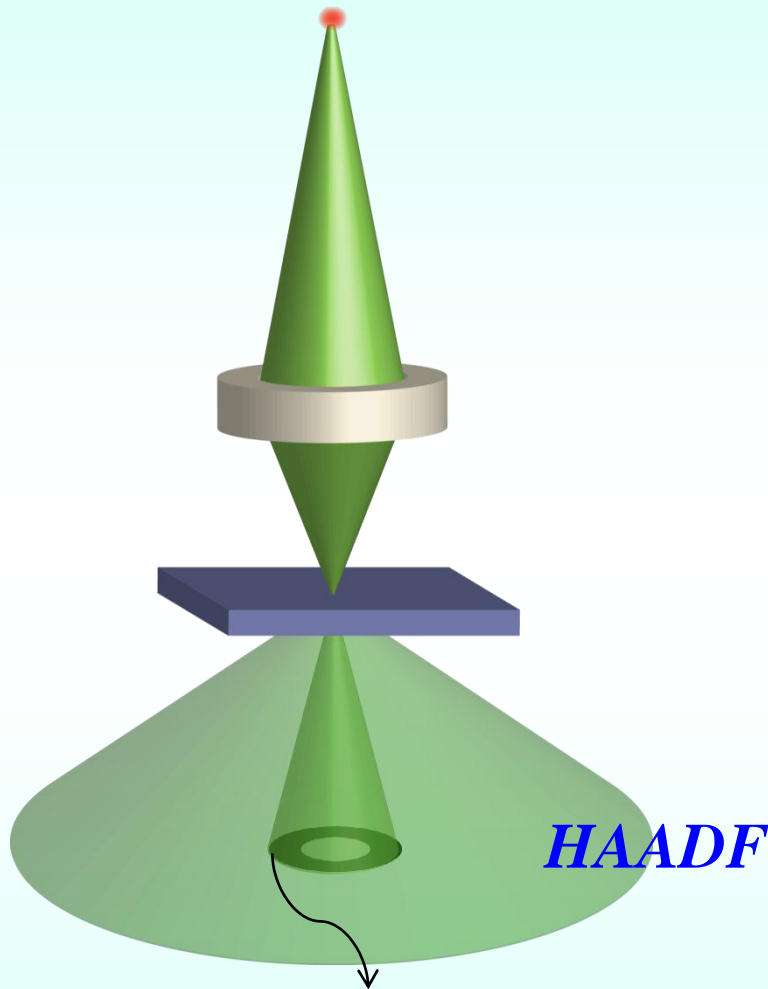
STEM: Annular Bright Field (ABF)

Findlay et al, APL (2009)

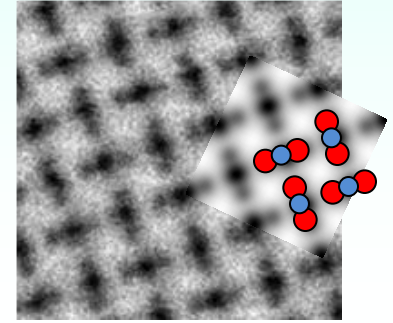
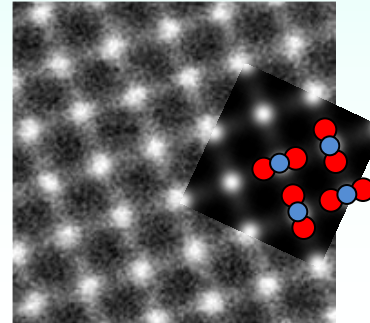
Okunishi et al, M&M (2009)

JEM ARM-200F, 200 keV, $\alpha = 22$ mrad

HAADF: 90–170 mrad, BF: 11–22 mrad

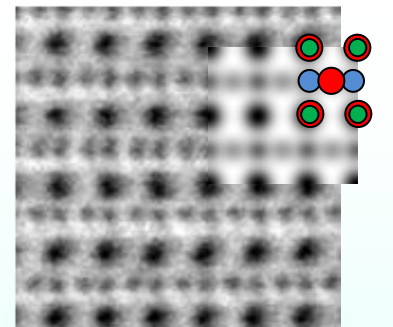
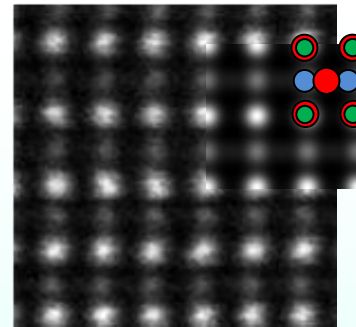


TiO_2 [001]



● O ● Ti ● Sr

SrTiO_3 [110]

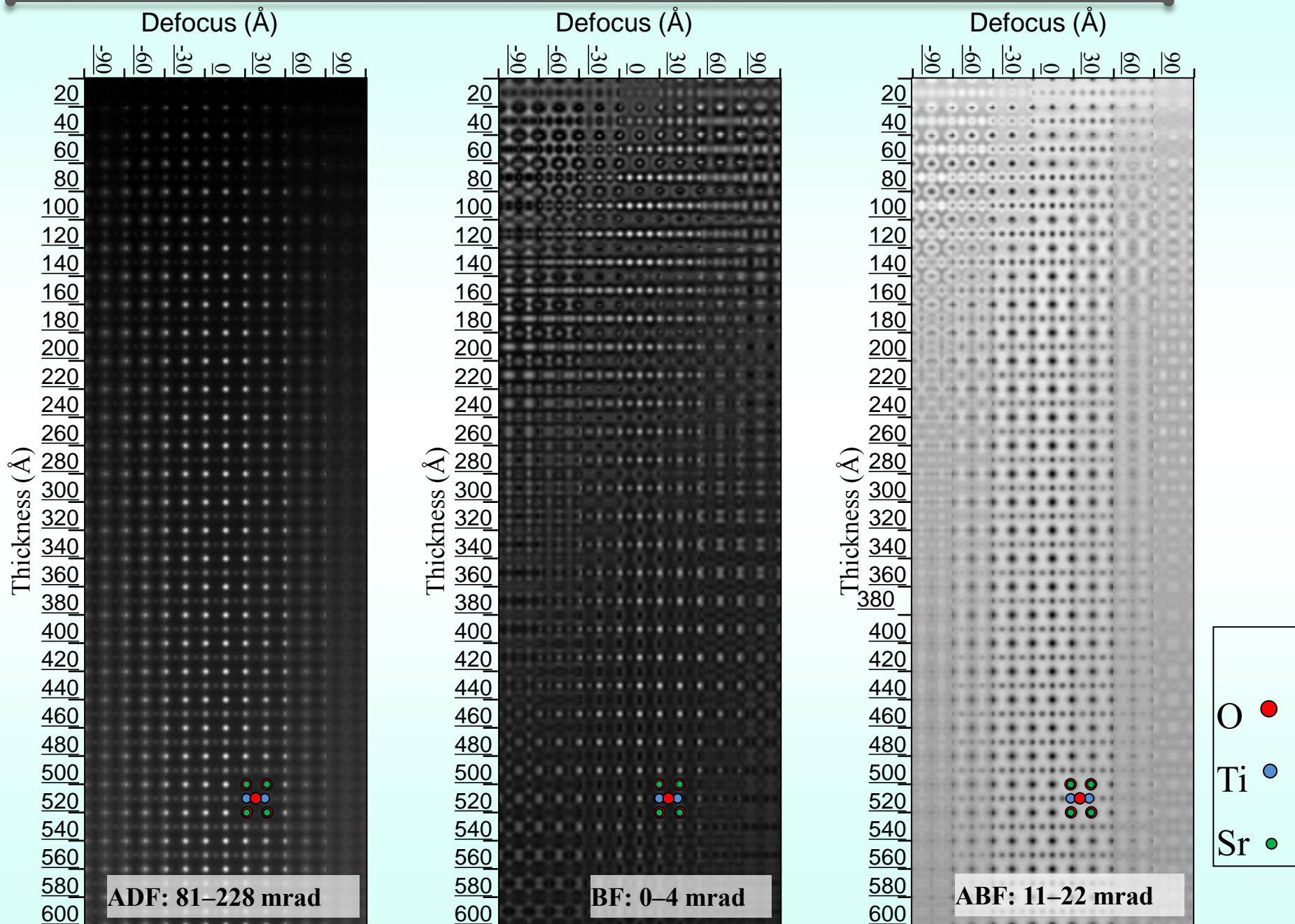


1 nm

*Annular bright field
(ABF) detector*

- ABF imaging shows light and heavy columns simultaneously.
- Seems to be robust over wide thickness range.

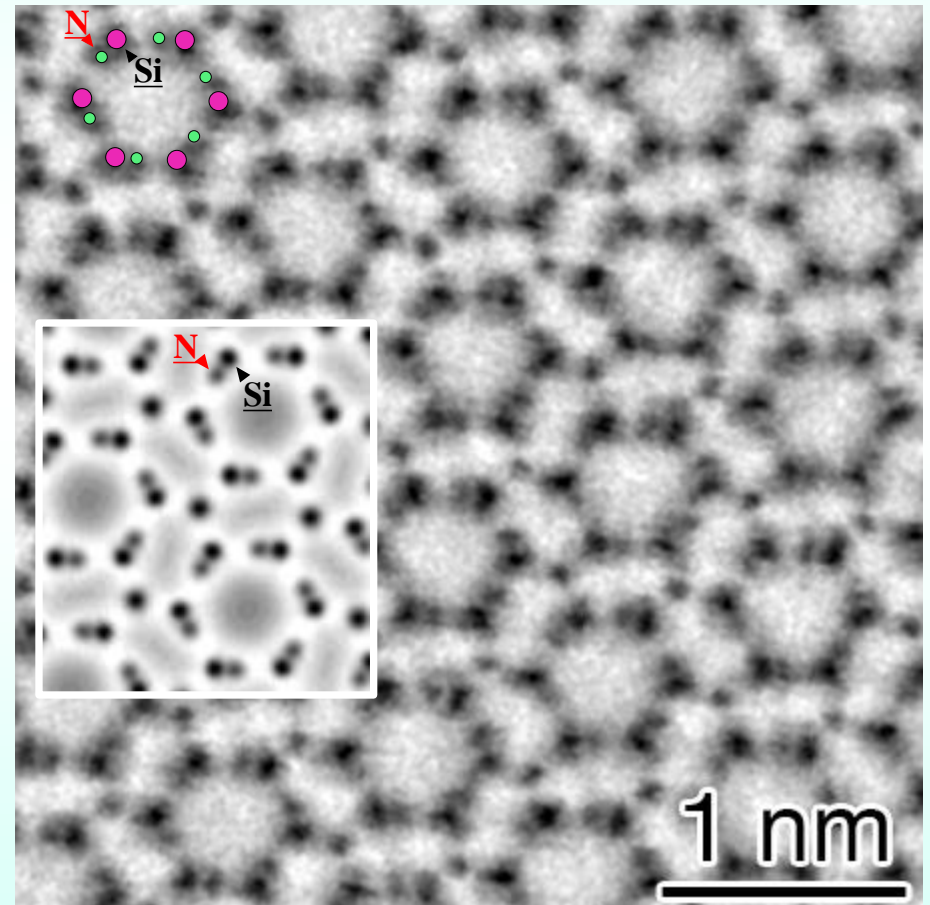
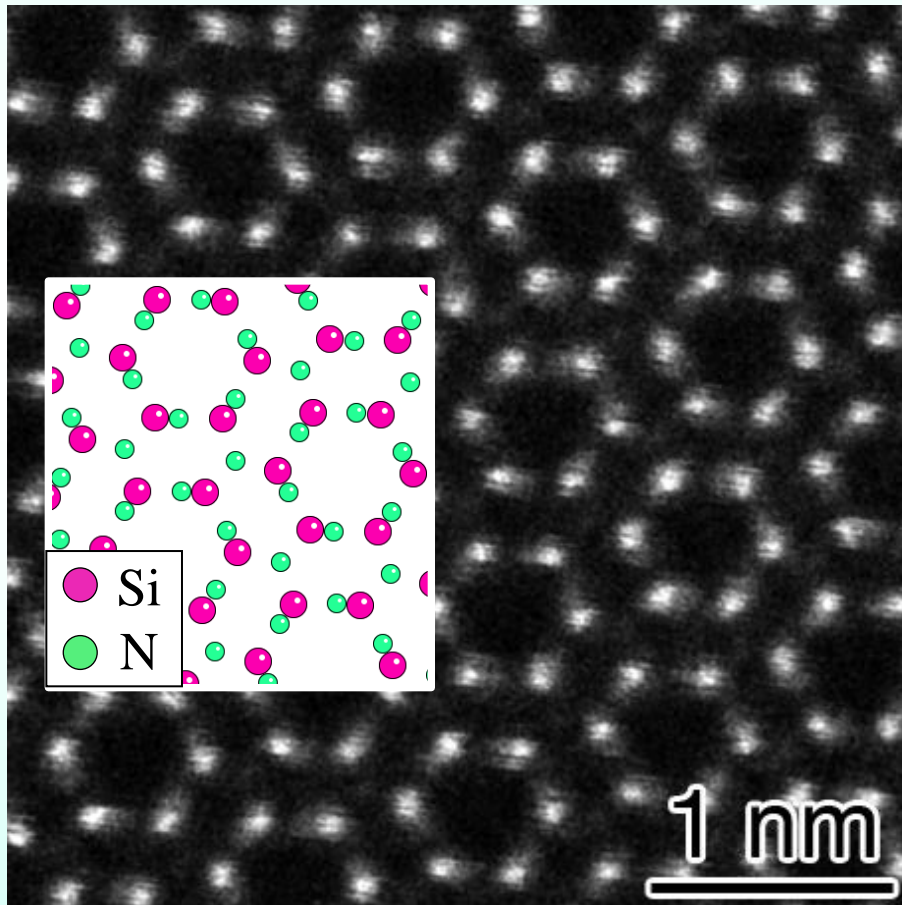
Defocus-thickness map simulations: SrTiO₃ [011]



STEM images of β -Si₃N₄ [0001]

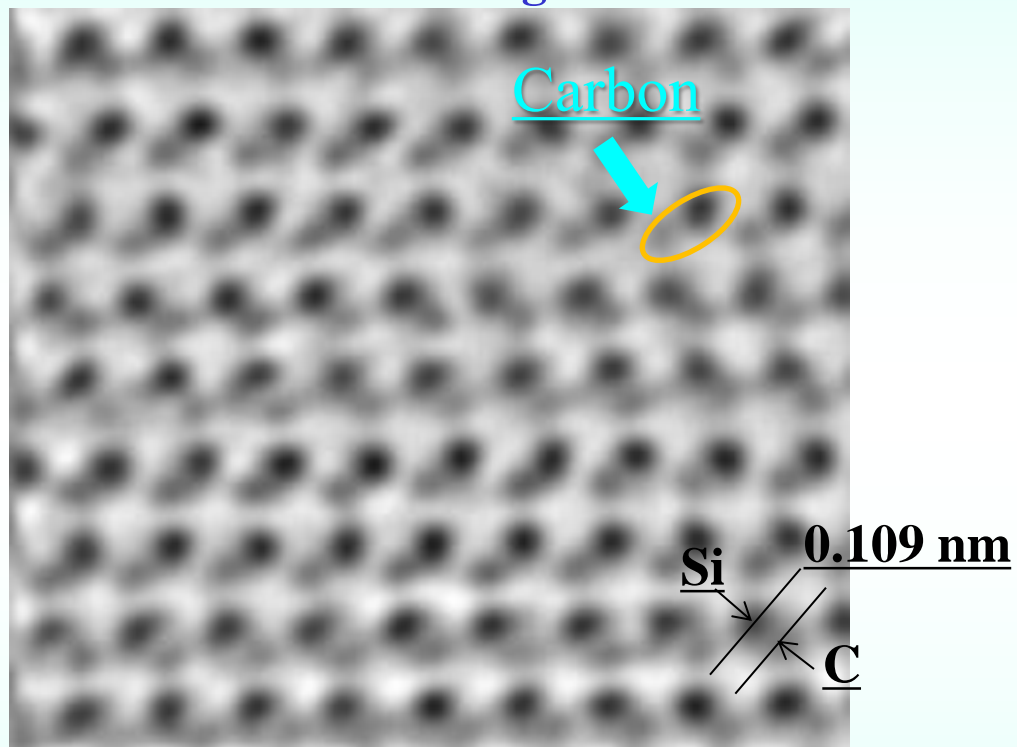
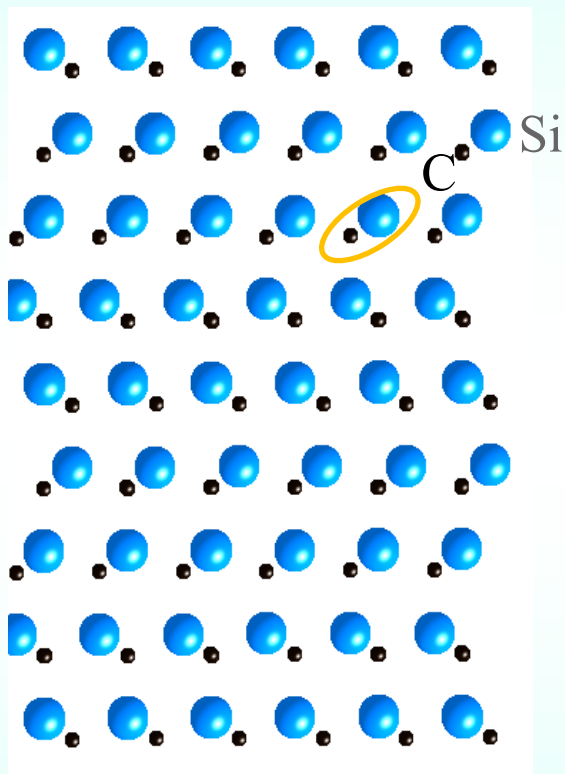
HAADF

ABF



4H-SiC [11 $\bar{2}$ 0] projection

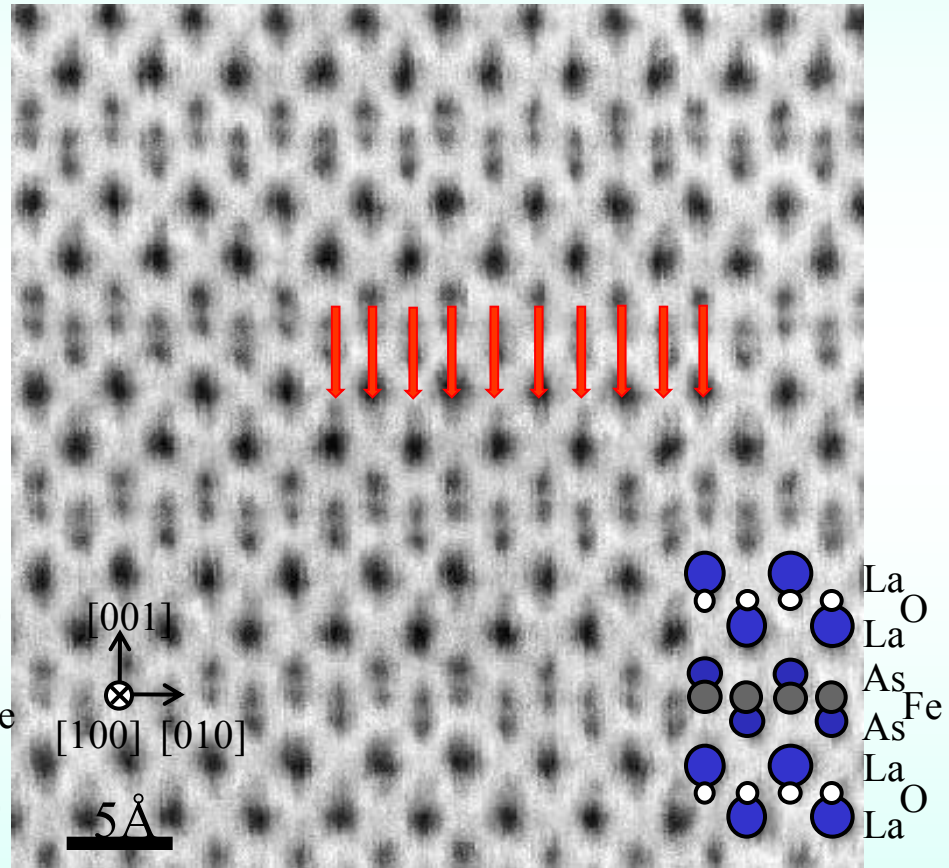
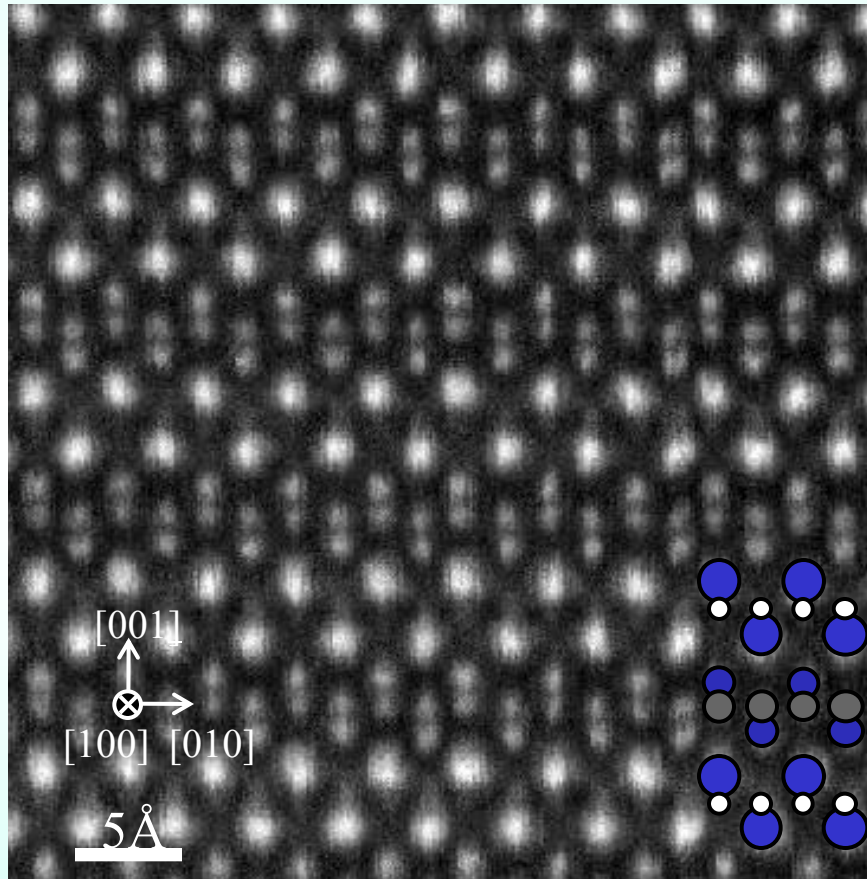
ABF STEM image



STEM Images of LaFeAsO_x

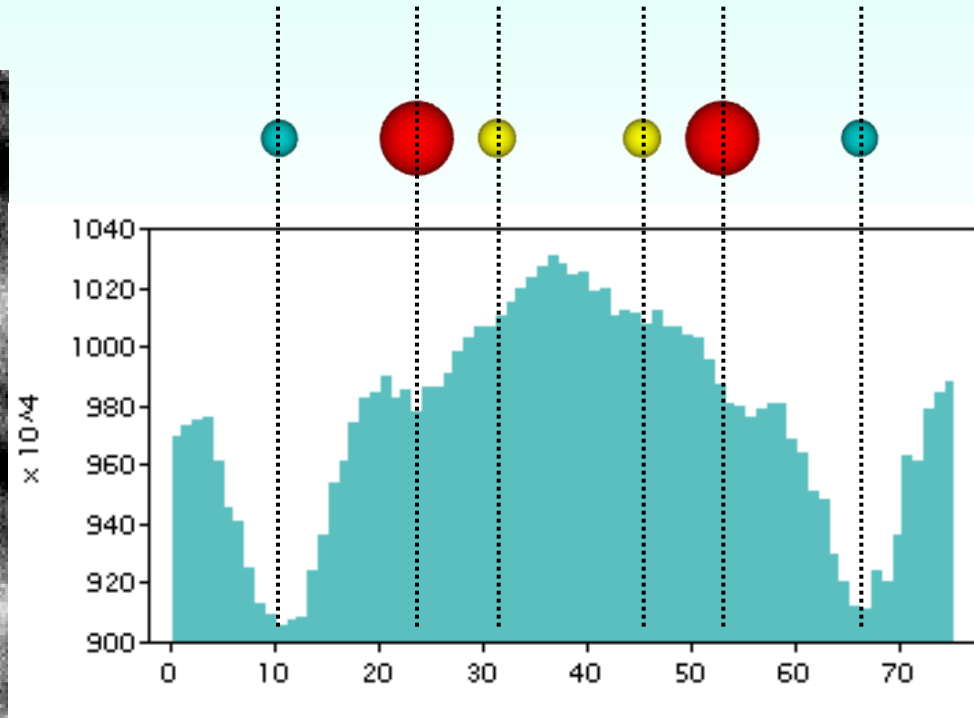
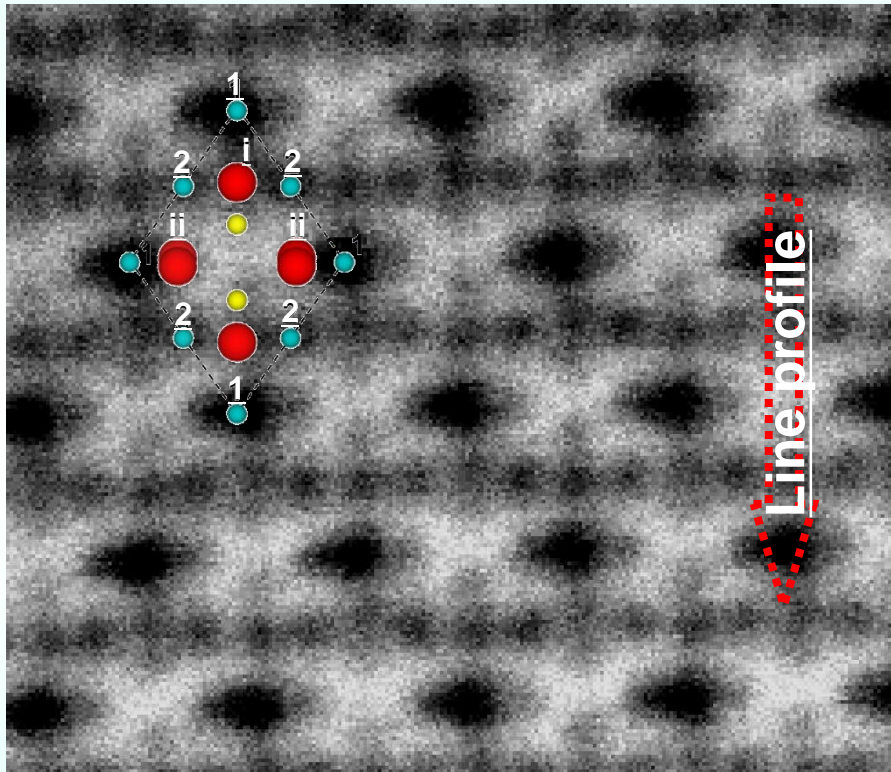
HAADF

ABF



Direct observation of Li in LiMn_2O_4 spinel by ABF technique in STEM

ABF: $\alpha=25$ mrad $\beta= 8-25$ mrad



Line profile

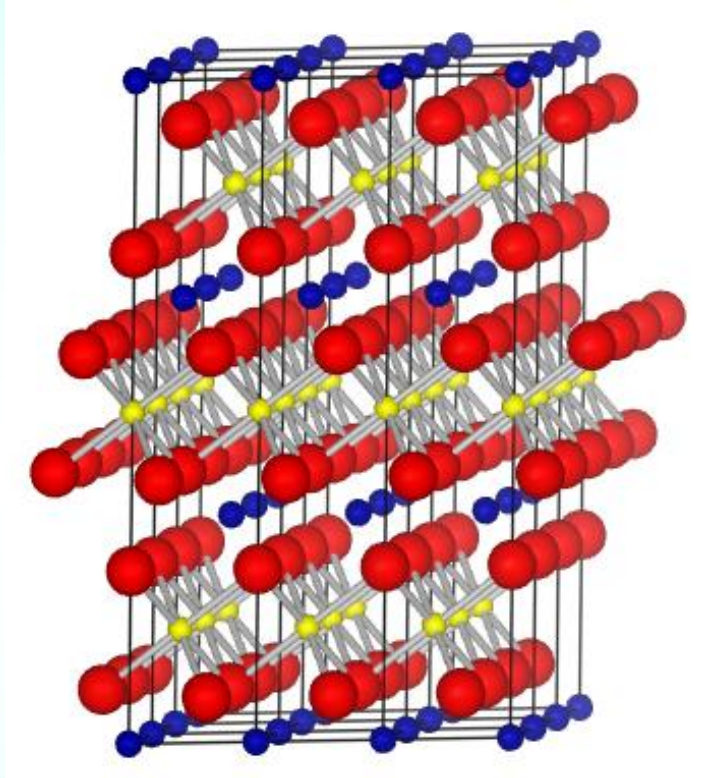


$[110]_{\text{LiMn}_2\text{O}_4}$

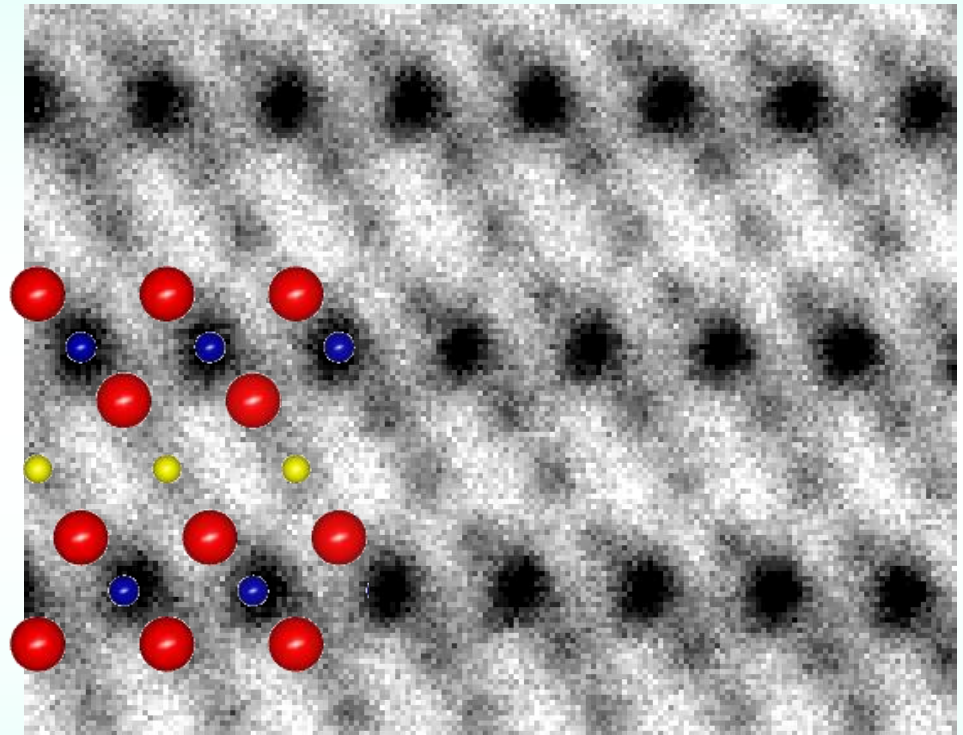
Direct observation of Li in LiCoO_2 by ABF technique in STEM

APL(2010)

ABF: $\alpha=25$ mrad $\beta= 8-25$ mrad



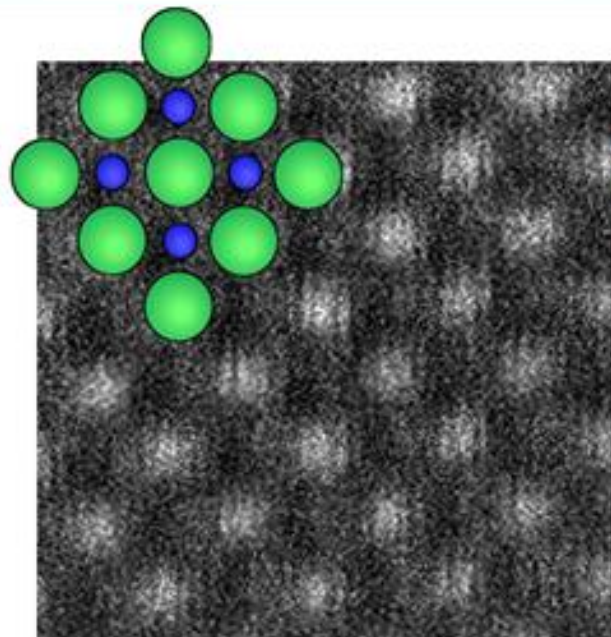
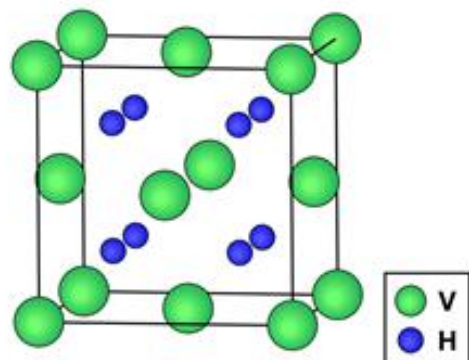
LiCoO_2 :
S.G. : R-3m (166)
 $a = b = 2.84 \text{ \AA}$, $c = 13.95 \text{ \AA}$



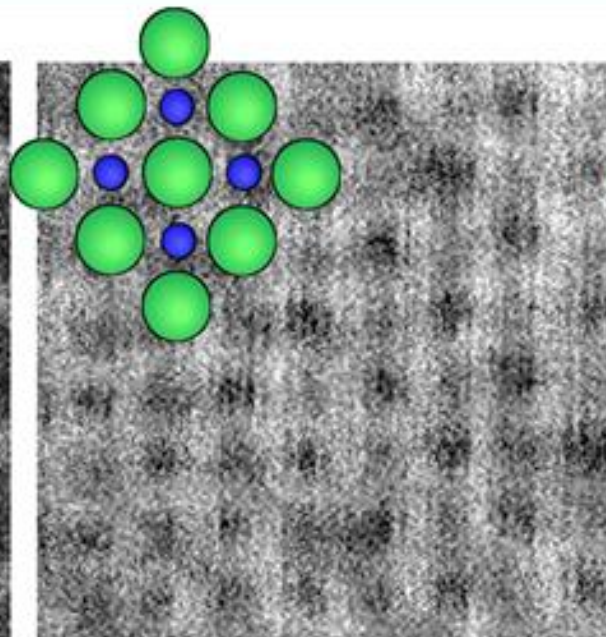
$[11\bar{2}0]_{\text{LiCoO}_2}$

Li can be clearly seen in this image

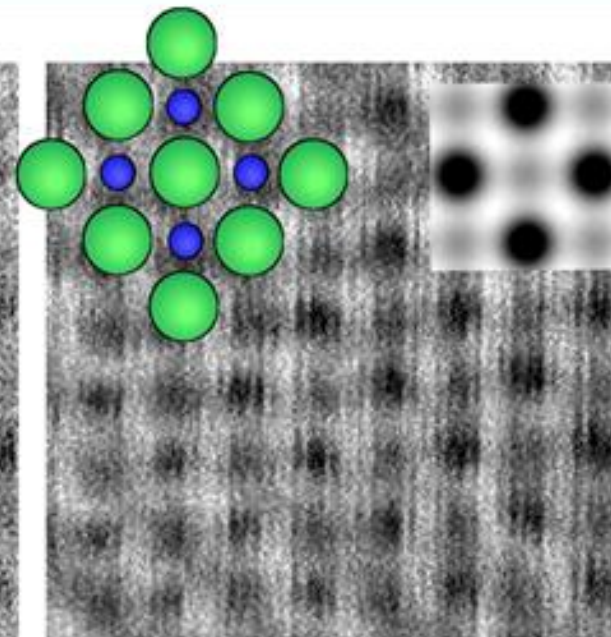
VH₂



HAADF



ABF



Filtered Image

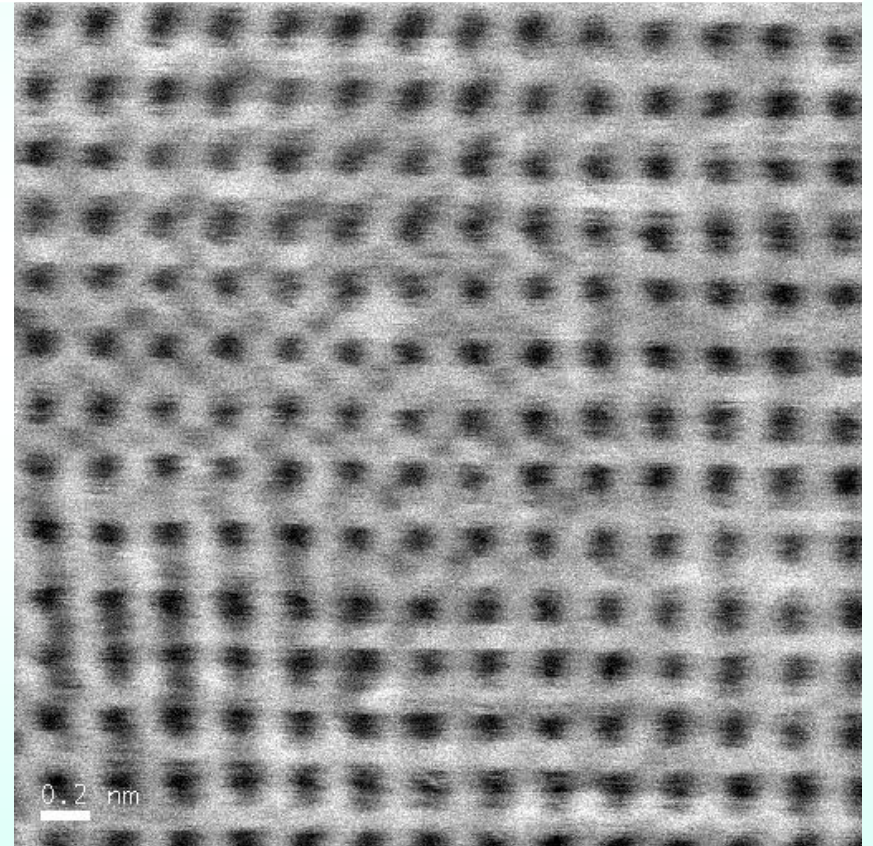
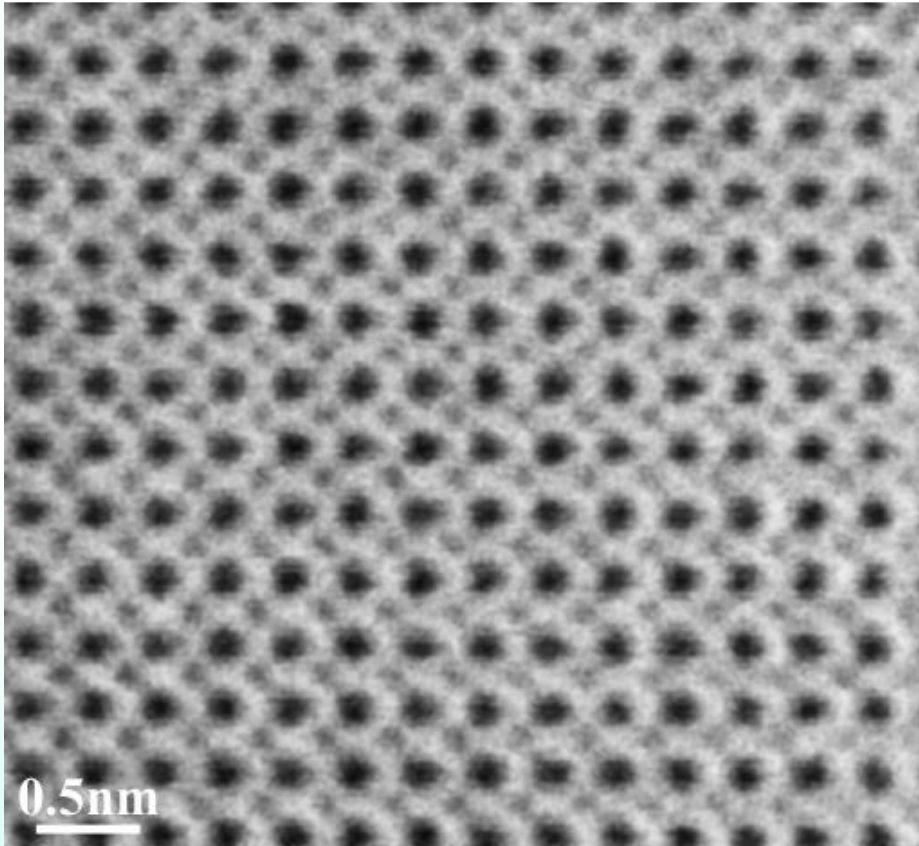
5Å

ABF-STEM Images

($\alpha = 25$ mrad, $\beta = 8-26$ mrad)

YH₂

TiH₂



High Resolution STEM + Quantitative Analysis

- Cs-corrected STEM (<1 Å)
- Theoretical Calculation (First Principles, Lattice Static, MO etc.)

- *Segregated Dopants at Ceramic Grain Boundaries,
Three Dimensional Observations, Single atom imaging ($\text{Al}_2\text{O}_3 : \text{Y}^{3+}$)
Super structure, Charge neutrality ($\text{Al}_2\text{O}_3 : \text{Ca}^{2++}\text{Si}^{4+}$)
Site of locally largest inter-atomic distance ($\text{ZnO}:\text{Pr}$)*
- *Catalyst (Au-nanoparticle on TiO_2), TiO_2 Surface
Small particles- Coherent interface*
- *STEM Annular Bright Field Imaging
Direct Observation of Li Ions and H (LiMn_2O_4 , LiCoO_2 , VH_2)*

Thank you for your attention!

Univ. Tokyo



JFCC(Nagoya)



WPI, Tohoku Univ. (Sendai)



Thank you very much!